

## Prof.Dr. ŞEMSETTİN ALTINDAL

### Kişisel Bilgiler

E-posta: altundal@gazi.edu.tr

Web: <https://avesis.gazi.edu.tr/altundal>

### Eğitim Bilgileri

Doktora, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (Dr), Türkiye 1986 - 1994

Yüksek Lisans, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), Türkiye 1983 - 1985

Lisans, Fırat Üniversitesi, Fen Fakültesi, Fizik Bölümü, Türkiye 1978 - 1982

### Yaptığı Tezler

Doktora, Al-siox-psi aygıtların ve güneş pillerinin elektriksel karakteristikleri, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (Dr), 1993

Yüksek Lisans, Çok ince yapı teorisi, Gazi Üniversitesi, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), 1950

### Akademik Unvanlar / Görevler

Prof.Dr., Gazi Üniversitesi, Fen Fakültesi, Fizik Bölümü, 2011 - Devam Ediyor

Doç.Dr., Gazi Üniversitesi, Fen Fakültesi, Fizik Bölümü, 2005 - 2011

Yrd.Doç.Dr., Gazi Üniversitesi, Fen Fakültesi, Fizik Bölümü, 1994 - 2005

Araştırma Görevlisi, Gazi Üniversitesi, Fen Fakültesi, Fizik Bölümü, 1983 - 1994

### Yönetilen Tezler

ALTINDAL Ş., Au/(Ag-ZnO/PVP)/n-Si (MPS) SCHOTTKY ENGEL DİYOTLARIN HAZIRLANMASI VE ELEKTRİK İLE DİELEKTRİK ÖZELLİKLERİNİN FREKANS VE VOLTAJA BAĞLI İNCELENMESİ, Doktora, Ö.SEVGİLİ(Öğrenci), 2020

ALTINDAL Ş., USLU İ., Grafen katkılı p-tipi ve n-tipi termoelektrik nanokompozit malzeme üretimi ve karakterizasyonu, Yüksek Lisans, S.KOÇYİĞİT(Öğrenci), 2017

ALTINDAL Ş., Polimer arayüzey tabakalı ve tabakasız schottky engel diyotların elektriksel karakteristiklerinin karşılaştırılması, Doktora, Ç.BİLKAN(Öğrenci), 2016

ALTINDAL Ş., USLU İ., Zirkonyum oksit ve gadolinyum oksit tabanlı çeşitli metal oksit katkılı inorganik pigmentlerin çöz-pel tekniğiyle sentezi ve karakterizasyonu, Yüksek Lisans, A.AYTİMUR(Öğrenci), 2015

ALTINDAL Ş., Au/ZnO/n-GaAs (MIS) Schottky engel diyotların (SBDs) elektriksel karakteristiklerinin frekans ve voltaja bağlı incelenmesi, Yüksek Lisans, B.AKIN(Öğrenci), 2015

ALTINDAL Ş., Au/(%1 Grafen Katkılı)-Ca<sub>1.9</sub>pr<sub>0.1</sub>co<sub>4</sub>ox/N-Si Schottky Engel Diyotların Hazırlanması Ve Elektrik ile Dielektrik Özelliklerinin Sıcaklık Ve Frekansa Bağlı incelenmesi, H.Gökçen(Öğrenci), 2015

ALTINDAL Ş., USLU İ., Grafen, bor ve nadir toprak elementleriyle katkılanmış poliviniliden florür nanokompozit piezo malzemelerin üretimi ve karakterizasyonu, Yüksek Lisans, Y.BADALI(Öğrenci), 2015

ALTINDAL Ş., Au/n-GaAs Schottky diyotların hazırlanması ve akım-iletim mekanizmalarının geniş bir sıcaklık aralığında incelenmesi, Doktora, E.ÖZAVCI(Öğrenci), 2015

ALTINDAL Ş., Au/Ca<sub>3</sub>Co<sub>4</sub>Ga<sub>0,001</sub>Ox/n-Si yapılarında doğru ve ters beslem akım-voltaj (I-V) karakteristiklerinin 80-340 K sıcaklık aralığında incelenmesi, Doktora, E.MARIL(Öğrenci), 2015

ALTINDAL Ş., Au/(%1 grafen (GP) katkılı)-Ca<sub>1.9</sub>Pr<sub>0.1</sub>Co<sub>4</sub>O<sub>x</sub>/n-Si Schottky engel diyotların hazırlanması ve elektrik ile dielektrik özelliklerinin sıcaklık ve frekansa bağlı incelenmesi, Doktora, H.GÖKÇEN(Öğrenci), 2015

ALTINDAL Ş., Au/PVA:Zn/n-Si (MPS) yapıların hazırlanması ve temel elektriksel özelliklerinin ışık altında incelenmesi, Doktora, U.AYDEMİR(Öğrenci), 2014

ALTINDAL Ş., Au/(Zn-Katkılı) polivinil alkol/n-GaAs yapıların hazırlanması ve akım-iletim mekanizmalarının geniş bir sıcaklık aralığında incelenmesi, Doktora, H.TECİMER(Öğrenci), 2014

ALTINDAL Ş., Metal-polimer-yarıiletken (MPS) yapıların elektrik ve dielektrik özelliklerinin geniş frekans aralığında incelenmesi, Doktora, A.KAYA(Öğrenci), 2013

ALTINDAL Ş., Au/n-4H-SiC (MS) schottky diyotların hazırlanması ve elektriksel karakteristiklerinin frekansa bağlı incelenmesi, Yüksek Lisans, Ö.SEVGİLİ(Öğrenci), 2013

ALTINDAL Ş., Perilensiz ve perilenli Al/p-Si schottky engel diyotların elektriksel özelliklerinin oda sıcaklığında karşılaştırılması, Yüksek Lisans, Ç.BİLKAN(Öğrenci), 2013

ALTINDAL Ş., Metal-yalıtkan-yarıiletken (Al/SiO<sub>2</sub>/p-Si) yapıların elektrik ve dielektrik özelliklerinin frekans ve potansiyele bağlı incelenmesi, Doktora, Z.SÖNMEZ(Öğrenci), 2012

ALTINDAL Ş., (Ni/Au)/Al<sub>0.22</sub>Ga<sub>0.78</sub>N/AlN/GaN çoklu-yapıların elektriksel karakteristiklerinin admitans spektroskopisi yöntemiyle incelenmesi, Doktora, Y.ŞAFAK(Öğrenci), 2012

ALTINDAL Ş., Au/PVA:Zn/n-Si (MPS)schottky engel diyodun elektriksel özelliklerinin sıcaklık ve radyasyona bağlı incelenmesi, Doktora, İ.TAŞÇIOĞLU(Öğrenci), 2012

ALTINDAL Ş., Au/(Bi-katkılı) polivinil alkol/n-si schottky engel diyotlarının elektriksel özelliklerinin sıcaklığa ve aydınlatma şiddetine bağlı incelenmesi, Yüksek Lisans, H.GÖKÇEN(Öğrenci), 2011

ALTINDAL Ş., Au/SiO<sub>2</sub>/n-Si (MIS) yapının elektrik ve dielektrik karakteristiklerinin sıcaklığa bağlı incelenmesi, Yüksek Lisans, A.GÜL(Öğrenci), 2011

ALTINDAL Ş., Al / Rhodamine - 101 / n-GaAs Schottky Engel diyotlarının hazırlanması ve iletim mekanizmalarının geniş bir sıcaklık aralığında incelenmesi, Doktora, Ö.VURAL(Öğrenci), 2011

ALTINDAL Ş., SiO<sub>2</sub>/p-Si (MIS) YAPILARIN ELEKTRİK KARAKTERİSTİKLERİNİN FREKANS BAĞLI İNCELENMESİ, A.KAYA(Öğrenci), 2010

ALTINDAL Ş., NiAu-AlGa<sub>n</sub>/Ga<sub>n</sub> heteroyapıların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Doktora, S.DEMİREZEN(Öğrenci), 2010

ALTINDAL Ş., NiAu-AlGa<sub>n</sub>/Ga<sub>n</sub> HETEROYAPILARIN ELEKTRİKSEL KARAKTERİSTİKLERİNİN SICAKLIĞA BAĞLI İNCELENMESİ, S.DEMİREZEN(Öğrenci), 2010

ALTINDAL Ş., Au/(Co, Zn-katkılı) polivinil alkol/n-Si schottky engel diyotlarının hazırlanması ve elektriksel özelliklerinin aydınlatma şiddetine bağlı incelenmesi, Doktora, H.USLU(Öğrenci), 2010

ALTINDAL Ş., Al/SiO<sub>2</sub>/p-Si (MIS) yapıların elektrik karakteristiklerinin frekansa bağlı incelenmesi, Yüksek Lisans, A.KAYA(Öğrenci), 2010

ALTINDAL Ş., Au/SrTiO<sub>3</sub>/n-Si (MFS) Schottky diyotların elektriksel parametrelerinin I-V, C-V ve DLTS metodu ile incelenmesi, Yüksek Lisans, U.AYDEMİR(Öğrenci), 2009

ALTINDAL Ş., Al/ SiO<sub>2</sub>/p-Si (MY) YAPILARIN AKIM-İLETİM MEKANİZMASI VE ELEKTRİKSEL ÖZELLİKLERİNİN SICAKLIĞA BAĞLI İNCELENMESİ, D.Esra(Öğrenci), 2008

ALTINDAL Ş., Au/SiO<sub>2</sub>/n-GaAs (MOY) yapıların elektrik ve dielektrik karakteristiklerinin frekans ve sıcaklığa bağlı incelenmesi, Doktora, M.GÖKÇEN(Öğrenci), 2008

ALTINDAL Ş., Al/SiO<sub>2</sub>/p-Si (MY) yapıların akım iletim mekanizması ve elektriksel özelliklerinin sıcaklığa bağlı incelenmesi, Doktora, D.ESRA(Öğrenci), 2008

ALTINDAL Ş., Yalıtkan tabakalı Al/p-Si Schottky diyotlarda elektriksel karakteristiklerin sıcaklığa bağlı incelenmesi, Doktora, H.KANBUR(Öğrenci), 2008

ALTINDAL Ş., Au/SiO<sub>2</sub>/n-GaAs (MOY) YAPILARIN ELEKTRİK VE DİELEKTRİK KARAKTERİSTİKLERİNİN FREKANS VE SICAKLIĞA BAĞLI İNCELENMESİ, M.GÖKÇEN(Öğrenci), 2008

ALTINDAL Ş., Metal-yalıtkan-yarı iletken (MIS) yapılarında elektrik ve dielektrik özelliklerinin sıcaklık ve frekansa bağlı incelenmesi, Doktora, İ.YÜCEDAĞ(Öğrenci), 2007

ALTINDAL Ş., Schottky diyotların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Yüksek Lisans, H.KUTLUCA(Öğrenci), 2007

ALTINDAL Ş., (Al-TiW+PtSi)/n-Si Schottky diyotların elektriksel özelliklerinin frekans ve aydınlanma şiddetine bağlı

incelenmesi, Yüksek Lisans, M.HAMDİ(Öğrenci), 2007

ALTINDAL Ş., Au/Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>/SiO<sub>2</sub>/n-Si (MFIS) YAPILARIN HAZIRLANMASI, ELEKTRİKSEL VE DİELEKTRİK ÖZELLİKLERİNİN FREKANS VESİCAKLİĞA BAĞLI İNCELENMESİ, F.PARLAKTÜRK(Öğrenci), 2007

ALTINDAL Ş., SCHOTTKY DİYOTLARIN ELEKTRİKSEL KARAKTERİSTİKLERİNİN SICAKLIĞA BAĞLI İNCELENMESİ, H.KUTLUCA(Öğrenci), 2007

ALTINDAL Ş., Au/Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>/SiO<sub>2</sub>/n-Si yapıların hazırlanması, elektriksel ve dielektrik özelliklerinin frekans ve sıcaklığa bağlı incelenmesi, Doktora, F.PARLAKTÜRK(Öğrenci), 2007

ALTINDAL Ş., MIS yapıların frekans ve radyasyona bağlı temel elektriksel parametreleri, Yüksek Lisans, B.TATAROĞLU(Öğrenci), 2006

ALTINDAL Ş., Doğal yalıtkan tabakalı Al/p-Si schottky diyotlarda elektriksel karakteristiklerin frekansa bağlı incelenmesi, Yüksek Lisans, H.KAMBUR(Öğrenci), 2005

ALTINDAL Ş., (Al-TiW+PtSi)/n-Si Schottky diyotlarının sıcaklığa bağlı temel parametreleri, Yüksek Lisans, E.MARIL(Öğrenci), 2005

ALTINDAL Ş., Doğal yalıtkan tabakalı Al/p-Si Schottky diyotlarda elektriksel karakteristiklerin frekansa bağlı incelenmesi, Yüksek Lisans, H.KANBUR(Öğrenci), 2005

ALTINDAL Ş., MOS yapılarda temel fiziksel parametrelerin frekans ve radyasyon miktarına bağlı incelenmesi, Doktora, A.TATAROĞLU(Öğrenci), 2004

ALTINDAL Ş., MOS yapılarda kapasitans-voltaj (C-V) ve iletkenlik voltaj (G/W-V) karakteristiklerinin frekans ve radyasyona bağlı incelenmesi, Yüksek Lisans, M.GÖKÇEN(Öğrenci), 2003

ALTINDAL Ş., Yalıtkan arayüzey tabakası ve seri dirence sahip Al/ SnO<sub>2</sub>/ p-Si schottky diyotların elektriksel karakteristiklerinin sıcaklığa bağlı incelenmesi, Yüksek Lisans, Z.TEKELİ(Öğrenci), 2002

ALTINDAL Ş., Al/p-Si ve Au/n-Si schottky diyotlarda I-V ve C-V karakteristiklerinin geniş bir sıcaklık aralığında analizi, Doktora, İ.DÖKME(Öğrenci), 2002

ALTINDAL Ş., Güneş pillerinde arayüzey durumlarının c.v. karakteristiklerine etkisi, Yüksek Lisans, E.YILDIZ(Öğrenci), 1999

ALTINDAL Ş., Metal-oksit-yarıiletken (MOS) kapasitörlerde dielektrik sabitinin frekans, sıcaklık ve kalınlığa bağlı incelenmesi, Yüksek Lisans, A.TATAROĞLU(Öğrenci), 1999

ALTINDAL Ş., Arayüz oksit tabakası ve seri dirence sahip ruln-Si schottky diyod parametrelerinin doğru beslem I-V ve C-V karakteristiklerinden hesaplanması, Yüksek Lisans, Ö.VURAL(Öğrenci), 1998

ALTINDAL Ş., Al-SiO<sub>2</sub>-pSi (MY) güneş pillerinin sıcaklığa bağlı elektriksel karakteristikleri, Yüksek Lisans, C.TEMEL(Öğrenci), 1997

## SCI, SSCI ve AHCI İndekslerine Giren Dergilerde Yayınlanan Makaleler

- I. **The effect of cadmium impurities in the (PVP-TeO<sub>2</sub>) interlayer in Al/p-Si (MS) Schottky barrier diodes (SBDs): Exploring its electrophysical parameters**  
Pirgholi-Givi G., ALTINDAL Ş., Shahedi Asl M., Sabahi Namini A., Farazin J., Azizian-Kalandaragh Y.  
Physica B: Condensed Matter, cilt.604, 2021 (SCI Expanded İndekslerine Giren Dergi)
- II. **Investigation of the variation of dielectric properties by applying frequency and voltage to Al/(CdS-PVA)/p-Si structures**  
Azizian-Kalandaragh Y., Yuçedag I., Demir G. E. , ALTINDAL Ş.  
Journal of Molecular Structure, cilt.1224, 2021 (SCI Expanded İndekslerine Giren Dergi)
- III. **Electrical characterization of Au/n-Si (MS) diode with and without graphene-polyvinylpyrrolidone (Gr-PVP) interface layer**  
TATAROĞLU A., ALTINDAL Ş., Azizian-Kalandaragh Y.  
Journal of Materials Science: Materials in Electronics, 2021 (SCI Expanded İndekslerine Giren Dergi)
- IV. **The reverse bias current-voltage-temperature (I-V-T) characteristics of the (Au/Ti)/Al<sub>2</sub>O<sub>3</sub>/n-GaAs Schottky barrier diodes (SBDs) in temperature range of 80-380 K**  
Guclu C. S. , Ozdemir A. F. , Aldemir D. A. , ALTINDAL Ş.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, 2021 (SCI İndekslerine Giren Dergi)

- V. **Current transport properties of (Au/Ni)/HfAlO<sub>3</sub>/n-Si metal-insulator-semiconductor junction**  
Arslan E., Badali Y., Aalizadeh M., ALTINDAL Ş., Ozbay E.  
JOURNAL OF PHYSICS AND CHEMISTRY OF SOLIDS, cilt.148, 2021 (SCI İndekslerine Giren Dergi)
- VI. **A Highly Sensitive Temperature Sensor Based on Au/Graphene-PVP/n-Si Type Schottky Diodes and the Possible Conduction Mechanisms in the Wide Range Temperatures**  
ÇİÇEK O., ALTINDAL Ş., Azizian-Kalandaragh Y.  
IEEE Sensors Journal, cilt.20, sa.23, ss.14081-14089, 2020 (SCI Expanded İndekslerine Giren Dergi)
- VII. **On the Multi-parallel Diodes Model in Au/PVA/n-GaAs Schottky Diodes and Investigation of Conduction Mechanisms (CMs) in a Temperature Range of 80-360 K**  
Evcin Baydilli E., Kaymaz A., Uslu Tecimer H., Altindal Ş.  
JOURNAL OF ELECTRONIC MATERIALS, cilt.49, sa.12, ss.7427-7434, 2020 (SCI İndekslerine Giren Dergi)
- VIII. **Effect of illumination on electrical parameters of Au/(P3DMTFT)/n-GaAs Schottky barrier diodes**  
Lapa H. E., KÖKCE A., ALDEMİR D. A., ÖZDEMİR A. F., ALTINDAL Ş.  
INDIAN JOURNAL OF PHYSICS, cilt.94, sa.12, ss.1901-1908, 2020 (SCI İndekslerine Giren Dergi)
- IX. **Detection of current transport mechanisms for graphene-doped-PVA interlayered metal/semiconductor structures**  
Baydilli E. E., Tan S. O., Tecimer H. U., Altindal Ş.  
PHYSICA B-CONDENSED MATTER, cilt.598, 2020 (SCI İndekslerine Giren Dergi)
- X. **On the electrical characteristics of Al/p-Si diodes with and without (PVP: Sn-TeO<sub>2</sub>) interlayer using current-voltage (I-V) measurements**  
Sabahi Namini A., Shahedi Asl M., Pirgholi-Givi G., Delbari S. A., Farazin J., ALTINDAL Ş., Azizian-Kalandaragh Y.  
Applied Physics A: Materials Science and Processing, cilt.126, sa.12, 2020 (SCI Expanded İndekslerine Giren Dergi)
- XI. **The interfacial properties of Au/n-4H-SiC structure with (Zn-doped PVA) interfacial layer**  
Lapa H. E., KÖKCE A., ALDEMİR D. A., ÖZDEMİR A. F., ALTINDAL Ş.  
PHYSICA SCRIPTA, cilt.95, sa.11, 2020 (SCI İndekslerine Giren Dergi)
- XII. **The possible current-conduction mechanism in the Au/(CoSO<sub>4</sub>-PVP)/n-Si junctions**  
Elamen H., Badali Y., GÜNEŞER M. T., ALTINDAL Ş.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.31, sa.21, ss.18640-18648, 2020 (SCI İndekslerine Giren Dergi)
- XIII. **The determination of the temperature and voltage dependence of the main device parameters of Au/7%Gr-doped PVA/n-GaAs-type Schottky Diode (SD)**  
Evcin Baydilli E., Altindal Ş., Tecimer H., Kaymaz A., Uslu Tecimer H.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.31, sa.20, ss.17147-17157, 2020 (SCI İndekslerine Giren Dergi)
- XIV. **On the frequency and voltage-dependent main electrical parameters of the Au/ZnO/n-GaAs structures at room temperature by using various methods**  
Akin B., ALTINDAL Ş.  
PHYSICA B-CONDENSED MATTER, cilt.594, 2020 (SCI İndekslerine Giren Dergi)
- XV. **Investigation of effects on dielectric properties of different doping concentrations of Au/Gr-PVA/p-Si structures at 0.1 and 1 MHz at room temperature**  
Ersoz Demir G., Yuicedag I., ALTINDAL Ş.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.31, sa.19, ss.16324-16331, 2020 (SCI İndekslerine Giren Dergi)
- XVI. **A comparative study on the electrical properties and conduction mechanisms of Au/n-Si Schottky diodes with/without an organic interlayer**  
Eroglu A., DEMİREZEN S., Azizian-Kalandaragh Y., ALTINDAL Ş.  
Journal of Materials Science: Materials in Electronics, cilt.31, sa.17, ss.14466-14477, 2020 (SCI Expanded İndekslerine Giren Dergi)
- XVII. **The origin of anomalous peak and negative capacitance on dielectric behavior in the accumulation region in Au/(0.07 Zn-doped polyvinyl alcohol)/n-4H-SiC metal-polymer-semiconductor structures/diodes studied by temperature-dependent impedance measurements**

- Al-Dharob M. H. , KÖKCE A., ALDEMİR D. A. , ÖZDEMİR A. F. , ALTINDAL Ş.  
JOURNAL OF PHYSICS AND CHEMISTRY OF SOLIDS, cilt.144, 2020 (SCI İndekslerine Giren Dergi)
- XVIII. **Electric and dielectric parameters in Au/n-Si (MS) capacitors with metal oxide-polymer interlayer as function of frequency and voltage**  
DEMİREZEN S., Eroglu A., Azizian-Kalandaragh Y., ALTINDAL Ş.  
Journal of Materials Science: Materials in Electronics, cilt.31, sa.18, ss.15589-15598, 2020 (SCI Expanded İndekslerine Giren Dergi)
- XIX. **Electrical and dielectric properties of Al/(PVP: Zn-TeO<sub>2</sub>)/p-Si heterojunction structures using current-voltage (I-V) and impedance-frequency (Z-f) measurements**  
Azizian-Kalandaragh Y., Farazin J., ALTINDAL Ş., Asl M. S. , Pirgholi-Givi G., Delbari S. A. , Namini A. S.  
Applied Physics A: Materials Science and Processing, cilt.126, sa.8, 2020 (SCI Expanded İndekslerine Giren Dergi)
- XX. **Electrical characteristics of Au/PVP/n-Si structures using admittance measurements between 1 and 500 kHz**  
ALPTEKİN S., ALTINDAL Ş.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.31, sa.16, ss.13337-13343, 2020 (SCI İndekslerine Giren Dergi)
- XXI. **A comparison study regarding Al/p-Si and Al/(carbon nanofiber-PVP)/p-Si diodes: current/impedance-voltage (I/Z-V) characteristics**  
SEVGİLİ Ö., YILDIRIM M., Azizian-Kalandaragh Y., ALTINDAL Ş.  
Applied Physics A: Materials Science and Processing, cilt.126, sa.8, 2020 (SCI Expanded İndekslerine Giren Dergi)
- XXII. **Intersection behavior of the current-voltage (I-V) characteristics of the (Au/Ni)/HfAlO<sub>3</sub>/n-Si (MIS) structure depends on the lighting intensity**  
Arslan E., Badali Y., ALTINDAL Ş., ÖZBAY E.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.31, sa.16, ss.13167-13172, 2020 (SCI İndekslerine Giren Dergi)
- XXIII. **Electrical and photoresponse properties of CoSO<sub>4</sub>-PVP interlayer based MPS diodes**  
Tataroglu A., Altindal Ş., Azizian-Kalandaragh Y.  
Journal of Materials Science: Materials in Electronics, cilt.31, sa.14, ss.11665-11672, 2020 (SCI Expanded İndekslerine Giren Dergi)
- XXIV. **Investigation of gamma-irradiation effects on electrical characteristics of Al/(ZnO-PVA)/p-Si Schottky diodes using capacitance and conductance measurements**  
KAYMAZ A., Tecimer H. U. , Baydilli E. E. , ALTINDAL Ş.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.31, sa.11, ss.8349-8358, 2020 (SCI İndekslerine Giren Dergi)
- XXV. **Frequency-Dependent Admittance Analysis of Au/n-Si Structure with CoSO<sub>4</sub>-PVP Interfacial Layer**  
Tascioglu I., SEVGİLİ Ö., Azizian-Kalandaragh Y., ALTINDAL Ş.  
Journal of Electronic Materials, cilt.49, sa.6, ss.3720-3727, 2020 (SCI Expanded İndekslerine Giren Dergi)
- XXVI. **Investigation of the effect of different Bi<sub>2</sub>O<sub>3</sub>-x:PVA (x = Sm, Sn, Mo) thin insulator interface-layer materials on diode parameters**  
Badali Y., Azizian-Kalandaragh Y., USLU İ., ALTINDAL Ş.  
Journal of Materials Science: Materials in Electronics, cilt.31, sa.10, ss.8033-8042, 2020 (SCI Expanded İndekslerine Giren Dergi)
- XXVII. **C-V-f and G/ω-V-f characteristics of Au/(In<sub>2</sub>O<sub>3</sub>-PVP)/n-Si (MPS) structure**  
Tataroglu A., Altindal Ş., Azizian-Kalandaragh Y.  
Physica B: Condensed Matter, cilt.582, 2020 (SCI Expanded İndekslerine Giren Dergi)
- XXVIII. **Frequency and voltage dependence of barrier height, surface states, and series resistance in Al/Al<sub>2</sub>O<sub>3</sub>/p-Si structures in wide range frequency and voltage**  
Turk C. G. , TAN S. O. , ALTINDAL Ş., İNEM B.  
PHYSICA B-CONDENSED MATTER, cilt.582, 2020 (SCI İndekslerine Giren Dergi)
- XXIX. **The effects of (Bi<sub>2</sub>Te<sub>3</sub>-Bi<sub>2</sub>O<sub>3</sub>-TeO<sub>2</sub>-PVP) interfacial film on the dielectric and electrical features of Al/p-Si (MS) Schottky barrier diodes (SBDs)**

- ALTINDAL Ş., Farazin J., Pirgholi-Givi G., MARIL E., Azizian-Kalandaragh Y.  
Physica B: Condensed Matter, cilt.582, 2020 (SCI Expanded İndekslerine Giren Dergi)
- XXX. **Investigation of Dielectric Properties, Electric Modulus and Conductivity of the Au/Zn-Doped PVA/n-4H-SiC (MPS) Structure Using Impedance Spectroscopy Method**  
Lapa H. E., KÖKCE A., ÖZDEMİR A. F., ALTINDAL Ş.  
ZEITSCHRIFT FÜR PHYSIKALISCHE CHEMIE-INTERNATIONAL JOURNAL OF RESEARCH IN PHYSICAL CHEMISTRY & CHEMICAL PHYSICS, cilt.234, sa.3, ss.505-516, 2020 (SCI İndekslerine Giren Dergi)
- XXXI. **Ultrasound-Assisted Method for Preparation of Ag<sub>2</sub>S Nanostructures: Fabrication of Au/Ag<sub>2</sub>S-PVA/n-Si Schottky Barrier Diode and Exploring Their Electrical Properties**  
Badali Y., Azizian-Kalandaragh Y., Akhlaghi E. A., Altindal Ş.  
Journal of Electronic Materials, cilt.49, sa.1, ss.444-453, 2020 (SCI Expanded İndekslerine Giren Dergi)
- XXXII. **Comparison of electrical properties of MS and MPS type diode in respect of (In<sub>2</sub>O<sub>3</sub>-PVP) interlayer**  
TATAROĞLU A., ALTINDAL Ş., Azizian-Kalandaragh Y.  
Physica B: Condensed Matter, cilt.576, 2020 (SCI Expanded İndekslerine Giren Dergi)
- XXXIII. **Identifying of series resistance and interface states on rhenium/n-GaAs structures using C-V-T and G/-V-T characteristics in frequency ranged 50 kHz to 5 MHz**  
ÇİÇEK O., DURMUŞ H., ALTINDAL Ş.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.31, sa.1, ss.704-713, 2020 (SCI İndekslerine Giren Dergi)
- XXXIV. **Frequency Response of C-V and G/ω-V Characteristics of Au/(Nanographite-doped PVP)/n-Si Structures**  
Akbas A. M., ÇİÇEK O., ALTINDAL Ş., Azizian-Kalandaragh Y.  
Journal of Materials Science: Materials in Electronics, 2020 (SCI Expanded İndekslerine Giren Dergi)
- XXXV. **A Compare Study on Electrical Properties of MS Diodes with and Without CoFe<sub>2</sub>O<sub>4</sub>-PVP Interlayer**  
Tataroglu A., Buyukbas Ulsan A., Altindal Ş., Azizian-Kalandaragh Y.  
Journal of Inorganic and Organometallic Polymers and Materials, 2020 (SCI Expanded İndekslerine Giren Dergi)
- XXXVI. **Investigation of the efficiencies of the (SnO<sub>2</sub>-PVA) interlayer in Au/n-Si (MS) SDs on electrical characteristics at room temperature by comparison**  
BİLKAN Ç., Azizian-Kalandaragh Y., SEVGİLİ Ö., ALTINDAL Ş.  
Journal of Materials Science: Materials in Electronics, cilt.30, sa.23, ss.20479-20488, 2019 (SCI Expanded İndekslerine Giren Dergi)
- XXXVII. **Determination of current transport and trap states density in AlInGaN/GaN heterostructures**  
Arslan E., Ural S., ALTINDAL Ş., ÖZBAY E.  
MICROELECTRONICS RELIABILITY, cilt.103, 2019 (SCI İndekslerine Giren Dergi)
- XXXVIII. **Dielectric properties of Ag/Ru-0.03-PVA/n-Si structures**  
Badali Y., Kocyigit S., USLU İ., ALTINDAL Ş.  
BULLETIN OF MATERIALS SCIENCE, cilt.42, sa.5, 2019 (SCI İndekslerine Giren Dergi)
- XXXIX. **Synthesis of boron and rare earth stabilized graphene doped polyvinylidene fluoride (PVDF) nanocomposite piezoelectric materials**  
Badali Y., Kocyigit S., Aytimur A., ALTINDAL Ş., USLU İ.  
POLYMER COMPOSITES, cilt.40, sa.9, ss.3623-3633, 2019 (SCI İndekslerine Giren Dergi)
- XL. **Dielectric characterization of BSA doped-PANI interlayered metal-semiconductor structures**  
KARAOĞLAN N., Tecimer H. U., ALTINDAL Ş., BİNDAL C.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.30, sa.15, ss.14224-14232, 2019 (SCI İndekslerine Giren Dergi)
- XLI. **Examination of dielectric response of Au/HgS-PVA/n-Si (MPS) structure by impedance spectroscopy method**  
SEVGİLİ Ö., Tascioglu I., Boughdachi S., Azizian-Kalandaragh Y., ALTINDAL Ş.  
Physica B: Condensed Matter, cilt.566, ss.125-135, 2019 (SCI Expanded İndekslerine Giren Dergi)
- XLII. **A comparative study on the electrical and dielectric properties of Al/Cd-doped ZnO/p-Si structures**  
Buyukbas-Ulsan A., Tascioglu I., Tataroglu A., Yakuphanoglu F., Altindal Ş.

- JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.30, sa.13, ss.12122-12129, 2019 (SCI İndekslerine Giren Dergi)
- XLIII. **The Structural and Electrical Properties of the Au/n-Si (MS) Diodes with Nanocomposites Interlayer (Ag-Doped ZnO/PVP) by Using the Simple Ultrasound-Assisted Method**  
Altındal Ş., Sevgili O., Azizian-Kalandaragh Y.  
IEEE Transactions on Electron Devices, cilt.66, sa.7, ss.3103-3109, 2019 (SCI Expanded İndekslerine Giren Dergi)
- XLIV. **Frequency, voltage and illumination interaction with the electrical characteristics of the CdZnO interlayered Schottky structure**  
Tascioglu I., Tan S. O. , Altındal Ş.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.30, sa.12, ss.11536-11541, 2019 (SCI İndekslerine Giren Dergi)
- XLV. **The study on negative dielectric properties of Al/PVA (Zn-doped)/p-Si (MPS) capacitors**  
Demirezen S., Tanrikulu E., Altındal Ş.  
INDIAN JOURNAL OF PHYSICS, cilt.93, sa.6, ss.739-747, 2019 (SCI İndekslerine Giren Dergi)
- XLVI. **Fabrication, structural and electrical characterization of Au/ (CuSe-polyvinyl alcohol)/n-Si (MPS) Schottky barrier structures**  
Mirzanezhad-Asl R., Phirouznia A., Altındal Ş., Badali Y., Azizian-Kalandaragh Y.  
Physica B: Condensed Matter, cilt.561, ss.1-8, 2019 (SCI Expanded İndekslerine Giren Dergi)
- XLVII. **On the possible conduction mechanisms in Rhenium/n-GaAs Schottky barrier diodes fabricated by pulsed laser deposition in temperature range of 60-400K**  
DURMUŞ H., YILDIRIM M., ALTINDAL Ş.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.30, sa.9, ss.9029-9037, 2019 (SCI İndekslerine Giren Dergi)
- XLVIII. **The fabrication of Al/p-Si (MS) type photodiode with (%2 ZnO-doped CuO) interfacial layer by sol gel method and their electrical characteristics**  
ÇETİNKAYA H. G. , SEVGİLİ Ö., ALTINDAL Ş.  
PHYSICA B-CONDENSED MATTER, cilt.560, ss.91-96, 2019 (SCI İndekslerine Giren Dergi)
- XLIX. **A comparative study on current/capacitance: voltage characteristics of Au/n-Si (MS) structures with and without PVP interlayer**  
ALPTEKİN S., ALTINDAL Ş.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.30, sa.7, ss.6491-6499, 2019 (SCI İndekslerine Giren Dergi)
- L. **Thermal Annealing Effects on the Electrical and Structural Properties of Ni/Pt Schottky Contacts on the Quaternary AlInGaN Epilayer**  
Arslan E., ALTINDAL Ş., Ural S., Kayal O. A. , Ozturk M., ÖZBAY E.  
JOURNAL OF ELECTRONIC MATERIALS, cilt.48, sa.2, ss.887-897, 2019 (SCI İndekslerine Giren Dergi)
- LI. **A comparison of electrical parameters of Au/n-Si and Au/(CoSO<sub>4</sub> -PVP)/n-Si structures (SBDs) to determine the effect of (CoSO<sub>4</sub> -PVP) organic interlayer at room temperature**  
ALTINDAL Ş., Sevgili O., Azizian-Kalandaragh Y.  
Journal of Materials Science: Materials in Electronics, 2019 (SCI Expanded İndekslerine Giren Dergi)
- LII. **Investigation of temperature dependent negative capacitance in the forward bias C-V characteristics of (Au/Ti)/Al<sub>2</sub>O<sub>3</sub>/n-GaAs Schottky barrier diodes (SBDs)**  
Guclu C. S. , Ozdemir A. F. , Karabulut A., Kokce A., Altındal Ş.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.89, ss.26-31, 2019 (SCI İndekslerine Giren Dergi)
- LIII. **Determination of Surface States Energy Density Distributions and Relaxation Times for a Metal-Polymer-Semiconductor Structure**  
ALPTEKİN S., TAN S. O. , ALTINDAL Ş.  
IEEE TRANSACTIONS ON NANOTECHNOLOGY, cilt.18, ss.1196-1199, 2019 (SCI İndekslerine Giren Dergi)
- LIV. **Current-Transport Mechanisms of the Al/(Bi<sub>2</sub>S<sub>3</sub>-PVA Nanocomposite)/p-Si Schottky Diodes in the Temperature Range Between 220 K and 380 K**  
Boughdachi S., Badali Y., Azizian-Kalandaragh Y., Altındal Ş.

- Journal of Electronic Materials, cilt.47, sa.12, ss.6945-6953, 2018 (SCI Expanded İndekslerine Giren Dergi)
- LIV. **Formation of ZnO nanopowders by the simple ultrasound-assisted method: Exploring the dielectric and electric properties of the Au/(ZnO-PVA)/n-Si structure**  
Nezhadesm-Kohardafchahi S., Farjami-Shayesteh S., Badali Y., Altindal Ş., Jamshidi-Ghozlu M. A. , Azizian-Kalandaragh Y.  
Materials Science in Semiconductor Processing, cilt.86, ss.173-180, 2018 (SCI Expanded İndekslerine Giren Dergi)
- LVI. **Temperature and Interfacial Layer Effects on the Electrical and Dielectric Properties of Al/(CdS-PVA)/p-Si (MPS) Structures**  
Demir G. E. , Yuçedag I., Azizian-Kalandaragh Y., ALTINDAL Ş.  
Journal of Electronic Materials, cilt.47, sa.11, ss.6600-6606, 2018 (SCI Expanded İndekslerine Giren Dergi)
- LVII. **Gaussian distribution in current-conduction mechanism of (Ni/Pt) Schottky contacts on wide bandgap AlInGaN quaternary alloy**  
Arslan E., ALTINDAL Ş., Ural S., Kayal O. A. , Ozturk M., ÖZBAY E.  
JOURNAL OF VACUUM SCIENCE & TECHNOLOGY B, cilt.36, sa.6, 2018 (SCI İndekslerine Giren Dergi)
- LVIII. **The investigation of current-conduction mechanisms (CCMs) in Au/(0.07Zn-PVA)/n-4H-SiC (MPS) Schottky diodes (SDs) by using (I-V-T) measurements**  
Al-Dharob M. H. , Lapa H. E. , Kokce A., Ozdemir A. F. , ALDEMİR D. A. , Altindal Ş.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.85, ss.98-105, 2018 (SCI İndekslerine Giren Dergi)
- LIX. **Preparation of mixed copper/PVA nanocomposites as an interface layer for fabrication of Al/Cu-PVA/p-Si Schottky structures**  
Akhlaghi E. A. , Badali Y., ALTINDAL Ş., Azizian-Kalandaragh Y.  
Physica B: Condensed Matter, cilt.546, ss.93-98, 2018 (SCI Expanded İndekslerine Giren Dergi)
- LX. **Effectuality of Barrier Height Inhomogeneity on the Current-Voltage-Temperature Characteristics of Metal Semiconductor Structures with CdZnO Interlayer**  
Tascioglu I., TAN S. O. , YAKUPHANOĞLU F., ALTINDAL Ş.  
JOURNAL OF ELECTRONIC MATERIALS, cilt.47, sa.10, ss.6059-6066, 2018 (SCI İndekslerine Giren Dergi)
- LXI. **Evaluation of Electric and Dielectric Properties of Metal-Semiconductor Structures With 2% GC-Doped-(Ca<sub>3</sub>Co<sub>4</sub>Ga<sub>0.0010x</sub>) Interlayer**  
MARIL E., TAN S. O. , ALTINDAL Ş., USLU İ.  
IEEE TRANSACTIONS ON ELECTRON DEVICES, cilt.65, sa.9, ss.3901-3908, 2018 (SCI İndekslerine Giren Dergi)
- LXII. **Integration of Zn-doped organic polymer nanocomposites between metal semiconductor structure to reveal the electrical qualifications of the diodes**  
Tecimer H. U. , Alper M. A. , Tecimer H., Tan S. O. , Altindal Ş.  
POLYMER BULLETIN, cilt.75, sa.9, ss.4257-4271, 2018 (SCI İndekslerine Giren Dergi)
- LXIII. **Determining electrical and dielectric parameters of Al/ZnS-PVA/p-Si (MPS) structures in wide range of temperature and voltage**  
BARAZ N., Yuçedag I., Azizian-Kalandaragh Y., ALTINDAL Ş.  
Journal of Materials Science: Materials in Electronics, cilt.29, sa.15, ss.12735-12743, 2018 (SCI Expanded İndekslerine Giren Dergi)
- LXIV. **Preparation of (CuS-PVA) interlayer and the investigation their structural, morphological and optical properties and frequency dependent electrical characteristics of Au/(CuS-PVA)/n-Si (MPS) structures**  
ERBİLEN TANRIKULU E., ALTINDAL Ş., Azizian-Kalandaragh Y.  
Journal of Materials Science: Materials in Electronics, cilt.29, sa.14, ss.11801-11811, 2018 (SCI Expanded İndekslerine Giren Dergi)
- LXV. **Effects of a Thin Ru-Doped PVP Interface Layer on Electrical Behavior of Ag/n-Si Structures**  
Badali Y., Nikravan A., ALTINDAL Ş., USLU İ.  
JOURNAL OF ELECTRONIC MATERIALS, cilt.47, sa.7, ss.3510-3520, 2018 (SCI İndekslerine Giren Dergi)
- LXVI. **Dielectric properties, electrical modulus and current transport mechanisms of Au/ZnO/n-Si structures**  
Badali Y., ALTINDAL Ş., USLU İ.



- PROGRESS IN NATURAL SCIENCE-MATERIALS INTERNATIONAL, cilt.28, sa.3, ss.325-331, 2018 (SCI İndekslerine Giren Dergi)
- LXVII. **A comparative study on dielectric behaviours of Au/(Zn-doped PVA)/n-4H-SiC (MPS) structures with different interlayer thicknesses using impedance spectroscopy methods**  
Lapa H. E., KÖKCE A., ÖZDEMİR A. F., USLU İ., ALTINDAL Ş.  
BULLETIN OF MATERIALS SCIENCE, cilt.41, sa.3, 2018 (SCI İndekslerine Giren Dergi)
- LXVIII. **Manufacturing and electrical characterization of Al-doped ZnO-coated silicon nanowires**  
Kaya A., Polat K. G., Mayet A. S., Mao H., ALTINDAL Ş., Islam M. S.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.75, ss.124-129, 2018 (SCI İndekslerine Giren Dergi)
- LXIX. **On the anomalous peak and negative capacitance in the capacitance-voltage (C-V) plots of Al/(%7 Zn-PVA)/p-Si (MPS) structure**  
Tanrikulu E., Demirezen S., Altindal Ş., Uslu I.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.29, sa.4, ss.2890-2898, 2018 (SCI İndekslerine Giren Dergi)
- LXX. **Preparation and characterization of cross-linked poly (vinyl alcohol)-graphene oxide nanocomposites as an interlayer for Schottky barrier diodes**  
Badrinezhad L., BİLKAN Ç., Azizian-Kalandaragh Y., Nematollahzadeh A., Orak I., ALTINDAL Ş.  
International Journal of Modern Physics B, cilt.32, sa.1, 2018 (SCI Expanded İndekslerine Giren Dergi)
- LXXI. **On the conduction mechanisms of Au/(Cu2O-CuO-PVA)/n-Si (MPS) Schottky barrier diodes (SBDs) using current-voltage-temperature (I-V-T) characteristics**  
Uluslan A. B., TATAROĞLU A., Azizian-Kalandaragh Y., Altindal Ş.  
Journal of Materials Science: Materials in Electronics, cilt.29, sa.1, ss.159-170, 2018 (SCI Expanded İndekslerine Giren Dergi)
- LXXII. **Diode-to-diode variation in dielectric parameters of identically prepared metal-ferroelectric-semiconductor structures**  
Cetinkaya H. G., Yildirim M., Durmus P., Altindal Ş.  
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.728, ss.896-901, 2017 (SCI İndekslerine Giren Dergi)
- LXXIII. **On the Frequency and Voltage-Dependent Profiles of the Surface States and Series Resistance of Au/ZnO/n-Si Structures in a Wide Range of Frequency and Voltage**  
Nikravan A., Badali Y., ALTINDAL Ş., Uslu I., Orak I.  
JOURNAL OF ELECTRONIC MATERIALS, cilt.46, sa.10, ss.5728-5736, 2017 (SCI İndekslerine Giren Dergi)
- LXXIV. **Two-diode behavior in metal-ferroelectric-semiconductor structures with bismuth titanate interfacial layer**  
DURMUŞ P., ALTINDAL Ş.  
INTERNATIONAL JOURNAL OF MODERN PHYSICS B, cilt.31, sa.27, 2017 (SCI İndekslerine Giren Dergi)
- LXXV. **Interfacial layer thickness dependent electrical characteristics of Au/(Zn-doped PVA)/n-4H-SiC (MPS) structures at room**  
Lapa H. E., KÖKCE A., Al-Dharob M., Orak I., ÖZDEMİR A. F., ALTINDAL Ş.  
EUROPEAN PHYSICAL JOURNAL-APPLIED PHYSICS, cilt.80, sa.1, 2017 (SCI İndekslerine Giren Dergi)
- LXXVI. **Correlation between barrier height and ideality factor in identically prepared diodes of Al/Bi4Ti3O12/p-Si (MFS) structure with barrier inhomogeneity**  
Cetinkaya H. G., Yildirim M., Durmus P., Altindal Ş.  
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.721, ss.750-756, 2017 (SCI İndekslerine Giren Dergi)
- LXXVII. **The energy density distribution profile of interface traps and their relaxation times and capture cross sections of Au/GO-doped PrBaCoO nanoceramic/n-Si capacitors at room temperature**  
Demirezen S., Kaya A., Altindal Ş., Uslu I.  
POLYMER BULLETIN, cilt.74, sa.9, ss.3765-3781, 2017 (SCI İndekslerine Giren Dergi)
- LXXVIII. **Series resistance and interface states effects on the C-V and G/w-V characteristics in Au/(Co3O4-doped PVA)/n-Si structures at room temperature**  
Demirezen S., Orak I., Azizian-Kalandaragh Y., Altindal Ş.  
Journal of Materials Science: Materials in Electronics, cilt.28, sa.17, ss.12967-12976, 2017 (SCI Expanded

İndekslerine Giren Dergi)

- LXXXIX. **On the temperature dependent current transport mechanisms and barrier inhomogeneity in Au/SnO<sub>2</sub>-PVA/n-Si Schottky barrier diodes**  
Bilkan C., Badali Y., Fotouhi-Shablou S., Azizian-Kalantaragh Y., Altindal Ş.  
Applied Physics A: Materials Science and Processing, cilt.123, sa.8, 2017 (SCI Expanded İndekslerine Giren Dergi)
- LXXX. **Controlling the electrical characteristics of Au/n-Si structure with and without (biphenyl-CoPc) and (OHSubs-ZnPc) interfacial layers at room temperature**  
BARAZ N., Yucedag I., DEMİR A., Ersoez G., ALTINDAL Ş., KANDAZ M.  
POLYMERS FOR ADVANCED TECHNOLOGIES, cilt.28, sa.8, ss.952-957, 2017 (SCI İndekslerine Giren Dergi)
- LXXXI. **Investigation of frequency and voltage dependence surface states and series resistance profiles using admittance measurements in Al/p-Si with Co<sub>3</sub>O<sub>4</sub>-PVA interlayer structures**  
BİLKAN Ç., ALTINDAL Ş., Azizian-Kalantaragh Y.  
Physica B: Condensed Matter, cilt.515, ss.28-33, 2017 (SCI Expanded İndekslerine Giren Dergi)
- LXXXII. **Investigation of the C-V characteristics that provides linearity in a large reverse bias region and the effects of series resistance, surface states and interlayer in Au/n-Si/Ag diodes**  
BİLKAN Ç., ALTINDAL Ş.  
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.708, ss.464-469, 2017 (SCI İndekslerine Giren Dergi)
- LXXXIII. **Electrical characteristics of Au/n-Si (MS) Schottky Diodes (SDs) with and without different rates (graphene + Ca<sub>1.9</sub>Pr<sub>0.1</sub>Co<sub>4</sub>O<sub>x</sub>-doped poly(vinyl alcohol)) interfacial layer**  
Cetinkaya H. G. , Altindal Ş., Orak I., Uslu I.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.28, sa.11, ss.7905-7911, 2017 (SCI İndekslerine Giren Dergi)
- LXXXIV. **Investigation of photo-induced effect on electrical properties of Au/PPy/n-Si (MPS) type schottky barrier diodes**  
Ersoz G., Yucedag I., Bayrakdar S., ALTINDAL Ş., Gumus A.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.28, sa.9, ss.6413-6420, 2017 (SCI İndekslerine Giren Dergi)
- LXXXV. **Frequency Dependent Electrical and Dielectric Properties of Au/P3HT:PCBM:F4-TCNQ/n-Si Schottky Barrier Diode**  
Tascioglu I., ÖZMEN Ö. T. , Sagban H. M. , Yaglioglu E., Altindal Ş.  
JOURNAL OF ELECTRONIC MATERIALS, cilt.46, sa.4, ss.2379-2386, 2017 (SCI İndekslerine Giren Dergi)
- LXXXVI. **Electrical and Dielectric Properties of a n-Si Schottky Barrier Diode with Bismuth Titanate Interlayer: Effect of Temperature**  
Yildirim M., Sahin C., Altindal Ş., Durmus P.  
JOURNAL OF ELECTRONIC MATERIALS, cilt.46, sa.3, ss.1895-1901, 2017 (SCI İndekslerine Giren Dergi)
- LXXXVII. **Synthesis and characterization of pure and graphene (Gr)-doped organic/polymer nanocomposites to investigate the electrical and photoconductivity properties of Au/n-GaAs structures**  
Cicek O., Tecimer H. U. , Tan S. O. , Tecimer H., Orak I., Altindal Ş.  
COMPOSITES PART B-ENGINEERING, cilt.113, ss.14-23, 2017 (SCI İndekslerine Giren Dergi)
- LXXXVIII. **Frequency dependent C-V and G/omega-V characteristics on the illumination-induced Au/ZnO/n-GaAs Schottky barrier diodes**  
Tan S. O. , Tecimer H. U. , Cicek O., Tecimer H., Altindal Ş.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.28, sa.6, ss.4951-4957, 2017 (SCI İndekslerine Giren Dergi)
- LXXXIX. **Temperature dependence of characteristic parameters of the Au/C<sub>20</sub>H<sub>12</sub>/n-Si Schottky barrier diodes (SBDs) in the wide temperature range**  
Moraki K., Bengi S., Zeyrek S., Bulbul M. M. , Altindal Ş.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.28, sa.5, ss.3987-3996, 2017 (SCI İndekslerine Giren Dergi)
- XC. **Determining electrical and dielectric parameters of dependence as function of frequencies in Al/ZnS-PVA/p-Si (MPS) structures**

BARAZ N., Yuçedag I., Azizian-Kalandaragh Y., ALTINDAL Ş.

Journal of Materials Science: Materials in Electronics, cilt.28, sa.2, ss.1315-1321, 2017 (SCI Expanded İndekslerine Giren Dergi)

- XCI. **Double exponential I-V characteristics and double Gaussian distribution of barrier heights in (Au/Ti)/Al<sub>2</sub>O<sub>3</sub>/n-GaAs (MIS) type Schottky barrier diodes in wide temperature range**  
Guclu C. S. , ÖZDEMİR A. F. , ALTINDAL Ş.  
APPLIED PHYSICS A-MATERIALS SCIENCE & PROCESSING, cilt.122, sa.12, 2016 (SCI İndekslerine Giren Dergi)
- XCII. **Frequency and voltage dependence dielectric properties, ac electrical conductivity and electric modulus profiles in Al/Co<sub>3</sub>O<sub>4</sub>-PVA/p-Si structures**  
BİLKAN Ç., Azizian-Kalandaragh Y., ALTINDAL Ş., Shokrani-Havigh R.  
Physica B: Condensed Matter, cilt.500, ss.154-160, 2016 (SCI Expanded İndekslerine Giren Dergi)
- XCIII. **A Comparative Study on the Main Electrical Parameters of Au/n-Si, Au/Biphenyl-CuPc/n-Si/ and Au/Biphenylsub-CoPc/n-Si/ Type Schottky Barrier Diodes**  
DEMİR A., Yuçedag I., Ersoz G., ALTINDAL Ş., BARAZ N., KANDAZ M.  
JOURNAL OF NANOELECTRONICS AND OPTOELECTRONICS, cilt.11, sa.5, ss.620-625, 2016 (SCI İndekslerine Giren Dergi)
- XCIV. **Study on the Reverse Bias Carrier Transport Mechanism in Au/TiO<sub>2</sub>/n-4H-SiC Structure**  
Alialy S., Yildiz D. E. , Altindal Ş.  
JOURNAL OF NANOELECTRONICS AND OPTOELECTRONICS, cilt.11, sa.5, ss.626-630, 2016 (SCI İndekslerine Giren Dergi)
- XCV. **Evaluation of electrical and photovoltaic behaviours as comparative of Au/n-GaAs (MS) diodes with and without pure and graphene (Gr)-doped polyvinyl alcohol (PVA) interfacial layer under dark and illuminated conditions**  
Cicek O., Tecimer H. U. , Tan S. O. , Tecimer H., Altindal Ş., Uslu I.  
COMPOSITES PART B-ENGINEERING, cilt.98, ss.260-268, 2016 (SCI İndekslerine Giren Dergi)
- XCVI. **Electrical characterizations of Au/ZnO/n-GaAs Schottky diodes under distinct illumination intensities**  
Tan S. O. , Tecimer H. U. , Cicek O., Tecimer H., Orak I., Altindal Ş.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.27, sa.8, ss.8340-8347, 2016 (SCI İndekslerine Giren Dergi)
- XCVII. **Investigation of Electrical Characteristics in Al/CdS-PVA/p-Si (MPS) Structures Using Impedance Spectroscopy Method**  
Ersoz G., Yuçedag I., Azizian-Kalandaragh Y., Orak I., ALTINDAL Ş.  
IEEE Transactions on Electron Devices, cilt.63, sa.7, ss.2948-2955, 2016 (SCI Expanded İndekslerine Giren Dergi)
- XCVIII. **Frequency and Voltage-Dependent Dielectric Properties and AC Electrical Conductivity of (Au/Ti)/Al<sub>2</sub>O<sub>3</sub>/n-GaAs with Thin Al<sub>2</sub>O<sub>3</sub> Interfacial Layer at Room Temperature**  
Guclu C. S. , Ozdemir A. F. , Kokce A., Altindal Ş.  
ACTA PHYSICA POLONICA A, cilt.130, sa.1, ss.325-330, 2016 (SCI İndekslerine Giren Dergi)
- XCIX. **A comparative study on the electrical parameters of Au/n-Si Schottky diodes with and without interfacial (Ca<sub>1.9</sub>Pr<sub>0.1</sub>Co<sub>4</sub>O<sub>x</sub>) layer**  
Kaya A., Cetinkaya H. G. , Altindal Ş., Uslu I.  
INTERNATIONAL JOURNAL OF MODERN PHYSICS B, cilt.30, sa.16, 2016 (SCI İndekslerine Giren Dergi)
- C. **The comparative electrical characteristics of Au/n-Si (MS) diodes with and without a 2% graphene cobalt-doped Ca<sub>3</sub>Co<sub>4</sub>Ga<sub>0.001</sub>O<sub>x</sub> interfacial layer at room temperature**  
Kaya A., Maril E., Altindal Ş., Uslu I.  
MICROELECTRONIC ENGINEERING, cilt.149, ss.166-171, 2016 (SCI İndekslerine Giren Dergi)
- CI. **On the temperature dependent forward bias current-voltage (I-V) characteristics in Au/2% graphene-cobalt doped (Ca<sub>3</sub>Co<sub>4</sub>Ga<sub>0.001</sub>O<sub>x</sub>)/n-Si structure**  
Maril E., Kaya A., Cetinkaya H. G. , Kocyigit S., Altindal Ş.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.39, ss.332-338, 2015 (SCI İndekslerine Giren Dergi)
- CII. **Electrical and dielectric properties of Au/1% graphene (GP)+Ca<sub>1.9</sub>Pr<sub>0.1</sub>Co<sub>4</sub>O<sub>x</sub> doped poly(vinyl alcohol)/n-Si structures as function of temperature and voltage**

Cetinkaya H. G. , Kaya A., Altindal Ş., Kocyigit S.

CANADIAN JOURNAL OF PHYSICS, cilt.93, sa.10, ss.1213-1220, 2015 (SCI İndekslerine Giren Dergi)

- CIII. **Frequency and voltage dependence of electric and dielectric properties of Au/TiO<sub>2</sub>/n-4H-SiC (metal-insulator-semiconductor) type Schottky barrier diodes**  
Tanrikulu E., Yildiz D. E. , Gunen A., Altindal Ş.  
PHYSICA SCRIPTA, cilt.90, sa.9, 2015 (SCI İndekslerine Giren Dergi)
- CIV. **Comparative study of the temperature-dependent dielectric properties of Au/PPy/n-Si (MPS)-type Schottky barrier diodes**  
Gumus A., Ersoz G., Yuçedag I., Bayrakdar S., ALTINDAL Ş.  
JOURNAL OF THE KOREAN PHYSICAL SOCIETY, cilt.67, sa.5, ss.889-895, 2015 (SCI İndekslerine Giren Dergi)
- CV. **Investigation of negative dielectric constant in Au/1 % graphene (GP) doped-Ca<sub>1.9</sub>Pr<sub>0.1</sub>Co<sub>40x</sub>/n-Si structures at forward biases using impedance spectroscopy analysis**  
Cetinkaya H. G. , Alialy S., Altindal Ş., Kaya A., Uslu I.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, cilt.26, sa.5, ss.3186-3195, 2015 (SCI İndekslerine Giren Dergi)
- CVI. **The effect of Mo-doped PVC plus TCNQ interfacial layer on the electrical properties of Au/PVC plus TCNQ/p-Si structures at room temperature**  
Demirezen S., Kaya A., Vural O., Altindal Ş.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.33, ss.140-148, 2015 (SCI İndekslerine Giren Dergi)
- CVII. **Electronic transport of Au/(Ca<sub>1.9</sub>Pr<sub>0.1</sub>Co<sub>40x</sub>)/n-Si structures analysed over a wide temperature range**  
Alialy S., Kaya A., Maril E., Altindal Ş., Uslu I.  
PHILOSOPHICAL MAGAZINE, cilt.95, sa.13, ss.1448-1461, 2015 (SCI İndekslerine Giren Dergi)
- CVIII. **Dielectric properties and electric modulus of Au/PPy/n-Si (MPS) type Schottky barrier diodes (SBDS) as a function of frequency and applied bias voltage**  
Yuçedag I., Ersoz G., Gumus A., ALTINDAL Ş.  
INTERNATIONAL JOURNAL OF MODERN PHYSICS B, cilt.29, sa.13, 2015 (SCI İndekslerine Giren Dergi)
- CIX. **A compare of electrical characteristics in Al/p-Si (MS) and Al/C<sub>20</sub>H<sub>12</sub>/p-Si (MPS) type diodes using current-voltage (I-V) and capacitance-voltage (C-V) measurements**  
Bilkan C., Zeyrek S., San S. E. , Altindal Ş.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.32, ss.137-144, 2015 (SCI İndekslerine Giren Dergi)
- CX. **Investigation of dielectric relaxation and ac electrical conductivity using impedance spectroscopy method in (AuZn)/TiO<sub>2</sub>/p-GaAs(110) schottky barrier diodes**  
ŞAFAK ASAR Y., ASAR T., ALTINDAL Ş., ÖZÇELİK S.  
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.628, ss.442-449, 2015 (SCI İndekslerine Giren Dergi)
- CXI. **On the Anomalous Peak in the Forward Bias Capacitance and Dielectric Properties of the Al/Co-Doped (PVC plus TCNQ)/p-Si structures as Function of Temperature**  
Yuçedag I., Kaya A., Altindal Ş.  
JOURNAL OF NANOELECTRONICS AND OPTOELECTRONICS, cilt.10, sa.2, ss.173-178, 2015 (SCI İndekslerine Giren Dergi)
- CXII. **On the analysis of the leakage current in Au/Ca<sub>3</sub>Co<sub>4</sub>Ga<sub>0.0010x</sub>/n-Si structure in the temperature range of 80-340 K**  
Maril E., Kaya A., Kocyigit S., Altindal Ş.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.31, ss.256-261, 2015 (SCI İndekslerine Giren Dergi)
- CXIII. **Dielectric spectroscopy studies and ac electrical conductivity on (AuZn)/TiO<sub>2</sub>/p-GaAs(110) MIS structures**  
ŞAFAK ASAR Y., ASAR T., ALTINDAL Ş., ÖZÇELİK S.  
PHILOSOPHICAL MAGAZINE, cilt.95, sa.26, ss.2885-2898, 2015 (SCI İndekslerine Giren Dergi)
- CXIV. **Current-conduction mechanism in Au/n-4H-SiC Schottky barrier diodes**  
Kaya A., Sevgili O., Altindal Ş., Ozturk M. K.  
INDIAN JOURNAL OF PURE & APPLIED PHYSICS, cilt.53, sa.1, ss.56-65, 2015 (SCI İndekslerine Giren Dergi)

- CXV. **On the negative capacitance behavior in the forward bias of Au/n-4H-SiC (MS) and comparison between MS and Au/TiO<sub>2</sub>/n-4H-SiC (MIS) type diodes both in dark and under 200 W illumination intensity**  
Cetinkaya H. G. , Yildiz D. E. , Altindal Ş.  
INTERNATIONAL JOURNAL OF MODERN PHYSICS B, cilt.29, sa.1, 2015 (SCI İndekslerine Giren Dergi)
- CXVI. **Electrical and dielectric properties and intersection behavior of G/omega-V plots for Al/Co-PVA/p-Si (MPS) structures at temperatures below room temperature**  
Yucedag I., Kaya A., ALTINDAL Ş., USLU İ.  
JOURNAL OF THE KOREAN PHYSICAL SOCIETY, cilt.65, sa.12, ss.2082-2089, 2014 (SCI İndekslerine Giren Dergi)
- CXVII. **Current-transport mechanisms in gold/polypyrrole/n-silicon Schottky barrier diodes in the temperature range of 110-360 K**  
Gumus A., Altindal Ş.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.28, ss.66-71, 2014 (SCI İndekslerine Giren Dergi)
- CXVIII. **Electrical Characteristics of Au/PVA (x-doped)/n-Si: Comparison Study on the Effect of Dopant Type in PVA**  
Dökme İ., Altindal Ş.  
FIBERS AND POLYMERS, cilt.15, ss.2253-2259, 2014 (SCI İndekslerine Giren Dergi)
- CXIX. **On the frequency dependent negative dielectric constant behavior in Al/Co-doped (PVC plus TCNQ)/p-Si structures**  
Yucedag I., Kaya A., Altindal Ş.  
INTERNATIONAL JOURNAL OF MODERN PHYSICS B, cilt.28, sa.23, 2014 (SCI İndekslerine Giren Dergi)
- CXX. **Analysis of temperature dependent current-conduction mechanisms in Au/TiO<sub>2</sub>/n-4H-SiC (metal/insulator/semiconductor) type Schottky barrier diodes**  
Alialy S., Altindal Ş., Tanrikulu E., Yildiz D. E.  
JOURNAL OF APPLIED PHYSICS, cilt.116, sa.8, 2014 (SCI İndekslerine Giren Dergi)
- CXXI. **Investigation of Current-Voltage Characteristics and Current Conduction Mechanisms in Composites of Polyvinyl Alcohol and Bismuth Oxide**  
YILDIRIM M., GÖKÇEN M., TUNÇ T., USLU İ., ALTINDAL Ş.  
POLYMER ENGINEERING AND SCIENCE, cilt.54, sa.8, ss.1811-1816, 2014 (SCI İndekslerine Giren Dergi)
- CXXII. **Energy density distribution profiles of surface states, relaxation time and capture cross-section in Au/n-type 4H-SiC SBDs by using admittance spectroscopy method**  
Kaya A., Sevgili O., Altindal Ş.  
INTERNATIONAL JOURNAL OF MODERN PHYSICS B, cilt.28, sa.17, 2014 (SCI İndekslerine Giren Dergi)
- CXXIII. **The effect of frequency and temperature on capacitance/conductance-voltage (C/G-V) characteristics of Au/n-GaAs Schottky barrier diodes (SBDs)**  
Demirezen S., Ozavci E., Altindal Ş.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.23, ss.1-6, 2014 (SCI İndekslerine Giren Dergi)
- CXXIV. **The current-voltage and capacitance-voltage characteristics at high temperatures of Au Schottky contact to n-type GaAs**  
Ozerli H., Karteri I., KARATAŞ Ş., ALTINDAL Ş.  
MATERIALS RESEARCH BULLETIN, cilt.53, ss.211-217, 2014 (SCI İndekslerine Giren Dergi)
- CXXV. **Frequency and voltage-dependent electrical and dielectric properties of Al/Co-doped PVA/p-Si structures at room temperature**  
Yucedag I., Kaya A., ALTINDAL Ş., USLU İ.  
CHINESE PHYSICS B, cilt.23, sa.4, 2014 (SCI İndekslerine Giren Dergi)
- CXXVI. **Dielectric and optical properties of CdS-polymer nanocomposites prepared by the successive ionic layer adsorption and reaction (SILAR) method**  
Azizian-Kalandaragh Y., AYDEMİR U., ALTINDAL Ş.  
Journal of Electronic Materials, cilt.43, sa.4, ss.1226-1231, 2014 (SCI Expanded İndekslerine Giren Dergi)
- CXXVII. **Charge transport mechanisms and density of interface traps in MnZnO/p-Si diodes**  
Tascioglu I., Farooq W. A. , TURAN R., ALTINDAL Ş., YAKUPHANOĞLU F.

- JOURNAL OF ALLOYS AND COMPOUNDS, cilt.590, ss.157-161, 2014 (SCI İndekslerine Giren Dergi)
- CXXXVIII. **On the frequency and voltage dependence of admittance characteristics of Al/PTCDA/P-Si (MPS) type Schottky barrier diodes (SBDs)**  
Tecimer H., Uslu H., Alahmed Z. A. , Yakuphanoglu F., Altindal Ş.  
COMPOSITES PART B-ENGINEERING, cilt.57, ss.25-30, 2014 (SCI İndekslerine Giren Dergi)
- CXXXIX. **Electrical and dielectric properties of Al/p-Si and Al/perylene/p-Si type diodes in a wide frequency range**  
Kaya A., Zeyrek S., SAN S. E. , Altindal Ş.  
CHINESE PHYSICS B, cilt.23, sa.1, 2014 (SCI İndekslerine Giren Dergi)
- CXXX. **A detailed comparative study on the main electrical parameters of Au/n-Si and Au/PVA:Zn/n-Si Schottky barrier diodes**  
AYDEMİR U., Tascioglu I., ALTINDAL Ş., USLU İ.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.16, sa.6, ss.1865-1872, 2013 (SCI İndekslerine Giren Dergi)
- CXXXI. **Analyses of temperature-dependent interface states, series resistances, and AC electrical conductivities of Al/p-Si and Al/Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>/p-Si structures by using the admittance spectroscopy method**  
YILDIRIM M., DURMUŞ P., ALTINDAL Ş.  
CHINESE PHYSICS B, cilt.22, sa.10, 2013 (SCI İndekslerine Giren Dergi)
- CXXXII. **Controlling the electrical characteristics of Al/p-Si structures through Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> interfacial layer**  
Durmus P., Yildirim M., Altindal Ş.  
CURRENT APPLIED PHYSICS, cilt.13, sa.8, ss.1630-1636, 2013 (SCI İndekslerine Giren Dergi)
- CXXXIII. **Temperature dependent current-transport mechanism in Au/(Zn-doped)PVA/n-GaAs Schottky barrier diodes (SBDs)**  
Tecimer H., Turut A., Uslu H., Altindal Ş., Uslu I.  
SENSORS AND ACTUATORS A-PHYSICAL, cilt.199, ss.194-201, 2013 (SCI İndekslerine Giren Dergi)
- CXXXIV. **The effect of series resistance and interface states on the frequency dependent C-V and G/w-V characteristics of Al/perylene/p-Si MPS type Schottky barrier diodes**  
Zeyrek S., Acaroglu E., Altindal Ş., Birdogan S., Bulbul M. M.  
CURRENT APPLIED PHYSICS, cilt.13, sa.7, ss.1225-1230, 2013 (SCI İndekslerine Giren Dergi)
- CXXXV. **The effect of metal work function on the barrier height of metal/CdS/SnO<sub>2</sub>/In-Ga structures**  
Tascioglu I., ALTINDAL Ş., POLAT İ., BACAŞIZ E.  
CURRENT APPLIED PHYSICS, cilt.13, sa.7, ss.1306-1310, 2013 (SCI İndekslerine Giren Dergi)
- CXXXVI. **Photovoltaic characteristics of Au/PVA (Bi-doped)/n-Si Schottky barrier diodes (SBDs) at various temperatures**  
Cetinkaya H. G. , Tecimer H., Uslu H., Altindal Ş.  
CURRENT APPLIED PHYSICS, cilt.13, sa.6, ss.1150-1156, 2013 (SCI İndekslerine Giren Dergi)
- CXXXVII. **The origin of negative capacitance in Au/n-GaAs Schottky barrier diodes (SBDs) prepared by photolithography technique in the wide frequency range**  
Korucu D., TÜRÜT A., ALTINDAL Ş.  
CURRENT APPLIED PHYSICS, cilt.13, sa.6, ss.1101-1108, 2013 (SCI İndekslerine Giren Dergi)
- CXXXVIII. **Trapping levels in TiGaSe<sub>2</sub> single crystals**  
Ozdemir S., ALTINDAL Ş.  
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.566, ss.108-111, 2013 (SCI İndekslerine Giren Dergi)
- CXXXIX. **Frequency and Voltage Dependence of Dielectric Loss of MgB<sub>2</sub> Composites at Different Temperatures**  
Korucu D., Ertekin E., BELENLİ İ., ALTINDAL Ş.  
JOURNAL OF SUPERCONDUCTIVITY AND NOVEL MAGNETISM, cilt.26, sa.6, ss.2165-2170, 2013 (SCI İndekslerine Giren Dergi)
- CXL. **A study of polymer-derived erbia-doped Bi<sub>2</sub>O<sub>3</sub> nanocrystalline ceramic powders**  
Aytimur A., Tascioglu I., ARI M., USLU İ., DAĞDEMİR Y., Durmus S., ALTINDAL Ş.

- JOURNAL OF SOL-GEL SCIENCE AND TECHNOLOGY, cilt.66, sa.2, ss.317-323, 2013 (SCI İndekslerine Giren Dergi)
- CXLI. **A detailed study on current-voltage characteristics of Au/n-GaAs in wide temperature range**  
Ozavci E., Demirezen S., AYDEMİR U., Altındal Ş.  
SENSORS AND ACTUATORS A-PHYSICAL, cilt.194, ss.259-268, 2013 (SCI İndekslerine Giren Dergi)
- CXLII. **Origin of forward bias capacitance peak and intersection behavior of C and G/w of Ag/p-InP Schottky barrier diodes**  
Korucu D., Turut A., TURAN R., Altındal Ş.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.16, sa.2, ss.344-351, 2013 (SCI İndekslerine Giren Dergi)
- CXLIII. **Temperature dependence of forward and reverse bias current-voltage characteristics in Al-TiW-PtSi/n-Si Schottky barrier diodes with the amorphous diffusion barrier**  
Afandiyeva I. M., Demirezen S., Altındal Ş.  
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.552, ss.423-429, 2013 (SCI İndekslerine Giren Dergi)
- CXLIV. **The Main Electrical and Interfacial Properties of Benzotriazole and Fluorene Based Organic Devices**  
YILDIZ D. E., Apaydin D. H., Kaya E., ALTINDAL Ş., ÇIRPAN A.  
JOURNAL OF MACROMOLECULAR SCIENCE PART A-PURE AND APPLIED CHEMISTRY, cilt.50, sa.2, ss.168-174, 2013 (SCI İndekslerine Giren Dergi)
- CXLV. **On the Voltage and Frequency Distribution of Dielectric Properties and ac Electrical Conductivity in Al/SiO<sub>2</sub>/p-Si (MOS) Capacitors**  
Kaya A., ALTINDAL Ş., ŞAFAK ASAR Y., Sonmez Z.  
CHINESE PHYSICS LETTERS, cilt.30, sa.1, 2013 (SCI İndekslerine Giren Dergi)
- CXLVI. **Two diodes model and illumination effect on the forward and reverse bias I-V and C-V characteristics of Au/PVA (Bi-doped)/n-Si photodiode at room temperature**  
Demirezen S., Altındal Ş., Uslu I.  
CURRENT APPLIED PHYSICS, cilt.13, sa.1, ss.53-59, 2013 (SCI İndekslerine Giren Dergi)
- CXLVII. **Temperature dependent conductivity and structural properties of sol-gel prepared holmium doped Bi<sub>2</sub>O<sub>3</sub> nanoceramic powder**  
Tascioglu I., Ari M., Uslu I., Kocyigit S., Dagdemir Y., Corumlu V., Altındal Ş.  
CERAMICS INTERNATIONAL, cilt.38, sa.8, ss.6455-6460, 2012 (SCI İndekslerine Giren Dergi)
- CXLVIII. **Effects of interface states and series resistance on electrical properties of Al/nanostructure CdO/p-GaAs diode**  
Tascioglu I., SOYLU M., ALTINDAL Ş., Al-Ghamdi A. A., Yakuphanoglu F.  
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.541, ss.462-467, 2012 (SCI İndekslerine Giren Dergi)
- CXLIX. **Evaluation of lateral barrier height of inhomogeneous photolithography-fabricated Au/n-GaAs Schottky barrier diodes from 80 K to 320 K**  
Korucu D., Efeoglu H., Turut A., Altındal Ş.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.15, sa.5, ss.480-485, 2012 (SCI İndekslerine Giren Dergi)
- CL. **Schottky diode properties of CuInSe<sub>2</sub> films prepared by a two-step growth technique**  
Tecimer H., Aksu S., Uslu H., Atasoy Y., Bacaksiz E., Altındal Ş.  
SENSORS AND ACTUATORS A-PHYSICAL, cilt.185, ss.73-81, 2012 (SCI İndekslerine Giren Dergi)
- CLI. **On the profile of frequency dependent interface states and series resistance in Au/p-InP SBDs prepared with photolithography technique**  
Korucu D., Turut A., TURAN R., Altındal Ş.  
SCIENCE CHINA-PHYSICS MECHANICS & ASTRONOMY, cilt.55, sa.9, ss.1604-1612, 2012 (SCI İndekslerine Giren Dergi)
- CLII. **The effects of temperature, radiation, and illumination on current-voltage characteristics of Au/PVA(Co, Zn-doped)/n-Si Schottky diodes**  
DÖKME İ., ALTINDAL Ş., USLU İ.  
JOURNAL OF APPLIED POLYMER SCIENCE, cilt.125, sa.2, ss.1185-1192, 2012 (SCI İndekslerine Giren Dergi)
- CLIII. **Structural and electrical characterization of rectifying behavior in n-type/intrinsic ZnO-based**

## homojunctions

Yilmaz S., POLAT İ., ALTINDAL Ş., BACAŞIZ E.

MATERIALS SCIENCE AND ENGINEERING B-ADVANCED FUNCTIONAL SOLID-STATE MATERIALS, cilt.177, sa.8, ss.588-593, 2012 (SCI İndekslerine Giren Dergi)

- CLIV. **Frequency dependent dielectric properties and electrical conductivity of platinum silicide/Si contact structures with diffusion barrier**  
Afandiyeva I. M. , Bulbul M. M. , Altindal Ş., Bengi S.  
MICROELECTRONIC ENGINEERING, cilt.93, ss.50-55, 2012 (SCI İndekslerine Giren Dergi)
- CLV. **The effect of gamma irradiation on electrical and dielectric properties of Al-TiW-Pd<sub>2</sub>Si/n-Si Schottky diode at room temperature**  
DÖKME İ., ALTINDAL Ş.  
CURRENT APPLIED PHYSICS, cilt.12, sa.3, ss.860-864, 2012 (SCI İndekslerine Giren Dergi)
- CLVI. **The effect of gamma irradiation on electrical and dielectric properties of organic-based Schottky barrier diodes (SBDs) at room temperature**  
Uslu H., YILDIRIM M., ALTINDAL Ş., DURMUŞ P.  
RADIATION PHYSICS AND CHEMISTRY, cilt.81, sa.4, ss.362-369, 2012 (SCI İndekslerine Giren Dergi)
- CLVII. **On the temperature dependent dielectric properties, conductivity and resistivity of MIS structures at 1 MHz**  
Eroglu A., TATAROĞLU A., Altindal Ş.  
MICROELECTRONIC ENGINEERING, cilt.91, ss.154-158, 2012 (SCI İndekslerine Giren Dergi)
- CLVIII. **Illumination intensity effects on the dielectric properties of schottky devices with Co, Ni-doped PVA nanofibers as an interfacial layer**  
Dökme İ., Yıldız D. E. , Altindal Ş.  
ADVANCES IN POLYMER TECHNOLOGY, cilt.31, ss.63-70, 2012 (SCI İndekslerine Giren Dergi)
- CLIX. **The effect of PVA (Bi<sub>2</sub>O<sub>3</sub>-doped) interfacial layer and series resistance on electrical characteristics of Au/n-Si (110) Schottky barrier diodes (SBDs)**  
Gokcen M., Tunc T., Altindal Ş., Uslu I.  
CURRENT APPLIED PHYSICS, cilt.12, sa.2, ss.525-530, 2012 (SCI İndekslerine Giren Dergi)
- CLX. **Electrical and photocurrent characteristics of Au/PVA (Co-doped)/n-Si photoconductive diodes**  
Gokcen M., Tunc T., Altindal Ş., Uslu I.  
MATERIALS SCIENCE AND ENGINEERING B-ADVANCED FUNCTIONAL SOLID-STATE MATERIALS, cilt.177, sa.5, ss.416-420, 2012 (SCI İndekslerine Giren Dergi)
- CLXI. **Does fludarabine increase the incidence of sinusoidal obstruction syndrome when combined with Bu/Cy during conditioning?**  
Suyani E., Altindal Ş., Aki S. Z. , Sucak G. T.  
CLINICAL TRANSPLANTATION, cilt.26, sa.2, 2012 (SCI İndekslerine Giren Dergi)
- CLXII. **Temperature dependent negative capacitance behavior of Al/rhodamine-101/n-GaAs Schottky barrier diodes and R-s effects on the C-V and G/omega-V characteristics**  
VURAL Ö., ŞAFAK ASAR Y., Turut A., ALTINDAL Ş.  
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.513, ss.107-111, 2012 (SCI İndekslerine Giren Dergi)
- CLXIII. **On the energy distribution of interface states and their relaxation time profiles in Al/pentacene/p-GaAs heterojunction diode**  
ŞAFAK ASAR Y., SOYLU M., YAKUPHANOĞLU F., ALTINDAL Ş.  
JOURNAL OF APPLIED PHYSICS, cilt.111, sa.3, 2012 (SCI İndekslerine Giren Dergi)
- CLXIV. **Frequency and voltage dependence of negative capacitance in Au/SiO<sub>2</sub>/n-GaAs structures**  
Gokcen M., Altuntas H., Altindal Ş., Ozcelik S.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.15, sa.1, ss.41-46, 2012 (SCI İndekslerine Giren Dergi)
- CLXV. **Effect of series resistance and interface states on the I-V, C-V and G/omega-V characteristics in Au/Bi-doped polyvinyl alcohol (PVA)/n-Si Schottky barrier diodes at room temperature**  
Demirezen S., Sonmez Z., AYDEMİR U., Altindal Ş.  
CURRENT APPLIED PHYSICS, cilt.12, sa.1, ss.266-272, 2012 (SCI İndekslerine Giren Dergi)



- CLXVI. **The density of interface states and their relaxation times in Au/Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>/SiO<sub>2</sub>/n-Si(MFIS) structures**  
 Bulbul M. M. , Altindal Ş., Parlakturk F., TATAROĞLU A.  
 SURFACE AND INTERFACE ANALYSIS, cilt.43, sa.13, ss.1561-1565, 2011 (SCI İndekslerine Giren Dergi)
- CLXVII. **On the profile of frequency and voltage dependent interface states and series resistance in (Ni/Au)/Al<sub>0.22</sub>Ga<sub>0.78</sub>N/AlN/GaN heterostructures by using current-voltage (I-V) and admittance spectroscopy methods**  
 Demirezen S., Altindal Ş., Ozcelik S., Ozbay E.  
 MICROELECTRONICS RELIABILITY, cilt.51, sa.12, ss.2153-2162, 2011 (SCI İndekslerine Giren Dergi)
- CLXVIII. **Comparative Analysis of Temperature-Dependent Electrical and Dielectric Properties of an Al-TiW-Pd<sub>2</sub>Si/n-Si Schottky Device at Two Frequencies**  
 DÖKME İ., ALTINDAL Ş.  
 IEEE TRANSACTIONS ON ELECTRON DEVICES, cilt.58, sa.11, ss.4042-4048, 2011 (SCI İndekslerine Giren Dergi)
- CLXIX. **Forward and reverse bias current-voltage characteristics of Au/n-Si Schottky barrier diodes with and without SnO<sub>2</sub> insulator layer**  
 Gokcen M., Altindal Ş., Karaman M., AYDEMİR U.  
 PHYSICA B-CONDENSED MATTER, cilt.406, sa.21, ss.4119-4123, 2011 (SCI İndekslerine Giren Dergi)
- CLXX. **Comparison of Pre- and Post-therapy 18F-FDG PET/CT Findings with The Findings of Clinical Follow-up in Patients with Hodgkin Lymphoma**  
 Akdemir Ü. Ö. , Kapucu L. Ö. , Oz O., Suyani E., Tonyali O., Altindal Ş., Yagci M., Benekli M., Atasever T., Buyukberber S., et al.  
 EUROPEAN JOURNAL OF NUCLEAR MEDICINE AND MOLECULAR IMAGING, cilt.38, 2011 (SCI İndekslerine Giren Dergi)
- CLXXI. **Electrical characteristics of Au/n-GaAs structures with thin and thick SiO<sub>2</sub> dielectric layer**  
 Altuntas H., Altindal Ş., Corekci S., Ozturk M. K. , Ozcelik S.  
 SEMICONDUCTORS, cilt.45, sa.10, ss.1286-1290, 2011 (SCI İndekslerine Giren Dergi)
- CLXXII. **Negative Dielectric Constant and Electrical Conductivity of Au/n-Si (111) Schottky Barrier Diodes with PVA/Ni,Zn Interfacial Layer**  
 Tunc T., Dokme İ., Altindal Ş., Uslu I.  
 JOURNAL OF APPLIED POLYMER SCIENCE, cilt.122, sa.1, ss.265-272, 2011 (SCI İndekslerine Giren Dergi)
- CLXXIII. **Preparation and Dielectric Properties of Polyvinyl Alcohol (Co, Zn Acetate) Fiber/n-Si and Polyvinyl Alcohol (Ni, Zn Acetate)/n-Si Schottky Diodes**  
 TUNÇ T., Uslu H., ALTINDAL Ş.  
 FIBERS AND POLYMERS, cilt.12, sa.7, ss.886-892, 2011 (SCI İndekslerine Giren Dergi)
- CLXXIV. **FUZZY CONTROL OF SEMI-BATCH POLYMERIZATION REACTOR WITH GENETIC ALGORITHM**  
 ALTINTEN A., Altindal Ş., Erdogan S., HAPOĞLU H.  
 JOURNAL OF THE FACULTY OF ENGINEERING AND ARCHITECTURE OF GAZI UNIVERSITY, cilt.26, sa.3, ss.613-621, 2011 (SCI İndekslerine Giren Dergi)
- CLXXV. **Effect of Vanadium Substitution on the Dielectric Properties of Glass Ceramic Bi-2212 Superconductor**  
 Cavdar Ş., KORALAY H., Altindal Ş.  
 JOURNAL OF LOW TEMPERATURE PHYSICS, cilt.164, ss.102-114, 2011 (SCI İndekslerine Giren Dergi)
- CLXXVI. **Temperature dependent current-voltage (I-V) characteristics of Au/n-Si (1 1 1) Schottky barrier diodes with PVA(Ni,Zn-doped) interfacial layer**  
 TUNÇ T., ALTINDAL Ş., USLU İ., DÖKME İ., Uslu H.  
 MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.14, sa.2, ss.139-145, 2011 (SCI İndekslerine Giren Dergi)
- CLXXVII. **On the mechanism of current-transport in Cu/CdS/SnO<sub>2</sub>/In-Ga structures**  
 Uslu H., ALTINDAL Ş., POLAT İ., Bayrak H., BACAKSIZ E.  
 JOURNAL OF ALLOYS AND COMPOUNDS, cilt.509, sa.18, ss.5555-5561, 2011 (SCI İndekslerine Giren Dergi)
- CLXXVIII. **Effects of illumination on I-V, C-V and G/w-V characteristics of Au/n-CdTe Schottky barrier diodes**

- Kanbur H., Altindal Ş., Mammadov T., Safak Y.  
JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS, cilt.13, ss.713-718, 2011 (SCI İndekslerine Giren Dergi)
- CLXXIX. **The origin of anomalous peak and negative capacitance in the forward bias capacitance-voltage characteristics of Au/PVA/n-Si structures**  
ALTINDAL Ş., Uslu H.  
JOURNAL OF APPLIED PHYSICS, cilt.109, sa.7, 2011 (SCI İndekslerine Giren Dergi)
- CLXXX. **The Illumination Intensity and Applied Bias Voltage on Dielectric Properties of Au/Polyvinyl Alcohol (Co, Zn-Doped)/n-Si Schottky Barrier Diodes**  
Uslu H., ALTINDAL Ş., TUNÇ T., Uslu I., Mammadov T. S.  
JOURNAL OF APPLIED POLYMER SCIENCE, cilt.120, sa.1, ss.322-328, 2011 (SCI İndekslerine Giren Dergi)
- CLXXXI. **The Au/polyvinyl alcohol (Co, Zn-doped)/n-type silicon Schottky barrier devices**  
DÖKME İ., Tunc T., Uslu I., Altindal Ş.  
SYNTHETIC METALS, cilt.161, ss.474-480, 2011 (SCI İndekslerine Giren Dergi)
- CLXXXII. **On the profile of frequency dependent dielectric properties of (Ni/Au)/GaN/Al<sub>0.3</sub>Ga<sub>0.7</sub>N heterostructures**  
Tekeli Z., Gokcen M., Altindal Ş., Ozcelik S., Ozbay E.  
MICROELECTRONICS RELIABILITY, cilt.51, sa.3, ss.581-586, 2011 (SCI İndekslerine Giren Dergi)
- CLXXXIII. **Analysis of the forward and reverse bias I-V characteristics on Au/PVA: Zn/n-Si Schottky barrier diodes in the wide temperature range**  
Tascioglu I., AYDEMİR U., ALTINDAL Ş., KINACI B., ÖZÇELİK S.  
JOURNAL OF APPLIED PHYSICS, cilt.109, sa.5, 2011 (SCI İndekslerine Giren Dergi)
- CLXXXIV. **The Gaussian distribution of barrier height in Au/n-GaAs Schottky diodes at high temperatures**  
TATAROĞLU A., Altindal Ş., Pur F. Z., Ataseven T., Sezgin S.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.5, ss.438-442, 2011 (SCI İndekslerine Giren Dergi)
- CLXXXV. **On the energy distribution profile of interface states obtained by taking into account of series resistance in Al/TiO<sub>2</sub>/p-Si (MIS) structures**  
Pakma O., Serin N., Serin T., Altindal Ş.  
PHYSICA B-CONDENSED MATTER, cilt.406, sa.4, ss.771-776, 2011 (SCI İndekslerine Giren Dergi)
- CLXXXVI. **Temperature dependent admittance spectroscopy of GaAs/AlGaAs single-quantum-well laser diodes (SQWLDs)**  
Bengi A., Uslu H., Asar T., Altindal Ş., Cetin S. Ş., Mammadov T. S., Ozcelik S.  
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.509, sa.6, ss.2897-2902, 2011 (SCI İndekslerine Giren Dergi)
- CLXXXVII. **Electrical characterization of MS and MIS structures on AlGaN/AlN/GaN heterostructures**  
Arslan E., Butun S., ŞAFAK ASAR Y., Uslu H., Tascioglu I., ALTINDAL Ş., ÖZBAY E.  
MICROELECTRONICS RELIABILITY, cilt.51, sa.2, ss.370-375, 2011 (SCI İndekslerine Giren Dergi)
- :LXXXVIII. **Anomalous Peak in the Forward-Bias C-V Plot and Temperature-Dependent Behavior of Au/PVA (Ni,Zn-doped)/n-Si(111) Structures**  
TUNÇ T., ALTINDAL Ş., DÖKME İ., Uslu H.  
JOURNAL OF ELECTRONIC MATERIALS, cilt.40, sa.2, ss.157-164, 2011 (SCI İndekslerine Giren Dergi)
- CLXXXIX. **On the profile of temperature and voltage dependence of interface states and resistivity in Au/n-Si structure with 79 angstrom insulator layer thickness**  
Yildirim M., Eroglu A., Altindal Ş., Durmus P.  
JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS, cilt.13, ss.98-105, 2011 (SCI İndekslerine Giren Dergi)
- CXC. **The forward bias current density-voltage-temperature (J-V-T) characteristics of Al-SiO<sub>2</sub>-pSi (MIS) Schottky diodes**  
Ozdemir S., DÖKME İ., ALTINDAL Ş.  
INTERNATIONAL JOURNAL OF ELECTRONICS, cilt.98, sa.6, ss.699-712, 2011 (SCI İndekslerine Giren Dergi)
- CXCI. **A comparative study of the dielectric properties of Al/p-Si structures with 50 and 826 angstrom**

## **SiO<sub>2</sub> interfacial layer**

Yildiz D. E. , Altindal Ş.

JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS, cilt.13, ss.53-58, 2011 (SCI İndekslerine Giren Dergi)

- CXCII. **The dependence of electrical properties of Al/NphAOEMA/PEDOT-PSS/ITO structures on temperature**  
Sahingoz R., Cavus H. K. , Altindal Ş., Soykan C., Dokme İ.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.4, sa.12, ss.2132-2135, 2010 (SCI İndekslerine Giren Dergi)
- CXCIII. **Illumination effect on electrical characteristics of organic-based Schottky barrier diodes**  
Uslu H., ALTINDAL Ş., DÖKME İ.  
JOURNAL OF APPLIED PHYSICS, cilt.108, sa.10, 2010 (SCI İndekslerine Giren Dergi)
- CXCIV. **AC electrical conductivity and dielectric properties of Al/NphAOEMA/PEDOT-PSS/ITO structure at different temperatures**  
Sahingoz R., Cavus H. K. , Altindal Ş.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.4, sa.11, ss.1779-1782, 2010 (SCI İndekslerine Giren Dergi)
- CXCV. **Temperature and frequency dependent dielectric properties of Au/Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>/SiO<sub>2</sub>/Si (MFIS) structures**  
Altindal Ş., Parlakturk F., TATAROĞLU A., Bulbul M. M.  
JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS, cilt.12, sa.10, ss.2139-2144, 2010 (SCI İndekslerine Giren Dergi)
- CXCVI. **The Effect of Gamma Irradiation on Electrical Characteristics of Au/Polyvinyl Alcohol (Co, Zn-Doped)/n-Si Schottky Barrier Diodes**  
Tascioglu I., Uslu H., Altindal Ş., Durmus P., Dokme İ., Tunc T.  
JOURNAL OF APPLIED POLYMER SCIENCE, cilt.118, sa.1, ss.596-603, 2010 (SCI İndekslerine Giren Dergi)
- CXCVII. **The explanation of barrier height inhomogeneities in Au/n-Si Schottky barrier diodes with organic thin interfacial layer**  
Tascioglu I., AYDEMİR U., ALTINDAL Ş.  
JOURNAL OF APPLIED PHYSICS, cilt.108, sa.6, 2010 (SCI İndekslerine Giren Dergi)
- CXCVIII. **A comparative study on the electrical characteristics of Au/n-Si structures with anatase and rutile phase TiO<sub>2</sub> interfacial insulator layer**  
Bengi A., Aydemir U., Altindal Ş., Özen Y., Ozcelik S.  
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.505, ss.628-633, 2010 (SCI İndekslerine Giren Dergi)
- CXCIX. **Temperature and voltage dependent current-transport mechanisms in GaAs/AlGaAs single-quantum-well lasers**  
Uslu H., Bengi A., Cetin S. Ş. , AYDEMİR U., Altindal Ş., Aghaliyeva S. T. , Ozcelik S.  
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.507, sa.1, ss.190-195, 2010 (SCI İndekslerine Giren Dergi)
- CC. **Temperature dependent capacitance and conductance-voltage characteristics of Au/polyvinyl alcohol(Co,Zn)/n-Si Schottky diodes**  
Bulbul M. M. , Bengi S., Dokme İ., Altindal Ş., Tunc T.  
JOURNAL OF APPLIED PHYSICS, cilt.108, sa.3, 2010 (SCI İndekslerine Giren Dergi)
- CCI. **Temperature dependent dielectric properties of Schottky diodes with organic interfacial layer**  
Dokme İ., Tunc T., Altindal Ş., Uslu I.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.4, sa.8, ss.1225-1228, 2010 (SCI İndekslerine Giren Dergi)
- CCII. **The interface states and series resistance effects on the forward and reverse bias I-V, C-V and G/omega-V characteristics of Al-TiW-Pd<sub>2</sub>Si/n-Si Schottky barrier diodes**  
Uslu H., Altindal Ş., AYDEMİR U., Dokme İ., Afandiyeva I. M.  
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.503, sa.1, ss.96-102, 2010 (SCI İndekslerine Giren Dergi)
- CCIII. **Dielectric properties and ac electrical conductivity of MIS structures in the wide frequency and**

**temperature range**

Yildiz D. E. , Altindal Ş.

OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.4, sa.7, ss.1002-1007, 2010 (SCI İndekslerine Giren Dergi)

- CCIV. **Temperature dependent current-voltage (I-V) characteristics of Au/n-Si (111) Schottky barrier diodes (SBDs) with polyvinyl alcohol (Co, Ni-Doped) interfacial layer**  
Tunc T., Dokme İ., Altindal Ş., Uslu I.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.4, sa.7, ss.947-950, 2010 (SCI İndekslerine Giren Dergi)
- CCV. **Interface state density analyzing of Au/TiO<sub>2</sub>(rutile)/n-Si Schottky barrier diode**  
Altuntas H., Bengi A., Asar T., Aydemir U., Sarikavak B., Özen Y., Altindal Ş., Ozcelik S.  
SURFACE AND INTERFACE ANALYSIS, cilt.42, ss.1257-1260, 2010 (SCI İndekslerine Giren Dergi)
- CCVI. **The effect of insulator layer thickness on the main electrical parameters in (Ni/Au)/Al<sub>x</sub>Ga<sub>1-x</sub>N/AlN/GaN heterostructures**  
ALTINDAL Ş., ŞAFAK ASAR Y., Tascioglu I., ÖZBAY E.  
SURFACE AND INTERFACE ANALYSIS, cilt.42, ss.803-806, 2010 (SCI İndekslerine Giren Dergi)
- CCVII. **Illumination effect on I-V, C-V and G/w-V characteristics of Al-TiW-Pd<sub>2</sub>Si/n-Si structures at room temperature**  
Uslu H., Dokme İ., Afandiyeva I. M. , Altindal Ş.  
SURFACE AND INTERFACE ANALYSIS, cilt.42, ss.807-811, 2010 (SCI İndekslerine Giren Dergi)
- CCVIII. **Current-voltage characteristics of Al/Rhodamine-101/n-GaAs structures in the wide temperature range**  
Vural O., Safak Y., Altindal Ş., Turut A.  
CURRENT APPLIED PHYSICS, cilt.10, sa.3, ss.761-765, 2010 (SCI İndekslerine Giren Dergi)
- CCIX. **Temperature dependent negative capacitance behavior in (Ni/Au)/AlGa<sub>n</sub>/AlN/GaN heterostructures**  
Arslan E., ŞAFAK ASAR Y., ALTINDAL Ş., Kelekci O., ÖZBAY E.  
JOURNAL OF NON-CRYSTALLINE SOLIDS, cilt.356, ss.1006-1011, 2010 (SCI İndekslerine Giren Dergi)
- CCX. **The effects of series resistance on the forward bias I-V characteristics in Au/Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>/SnO<sub>2</sub> (MFM) structures**  
TATAROĞLU A., Altindal Ş., AYDEMİR U., Uslu H.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.4, sa.5, ss.616-619, 2010 (SCI İndekslerine Giren Dergi)
- CCXI. **The distribution of barrier heights in Au/n-Si Schottky barrier diodes from I-V-T measurements**  
Durmus P., Cuha B., Altindal Ş., AYDEMİR U.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.4, sa.4, ss.579-583, 2010 (SCI İndekslerine Giren Dergi)
- CCXII. **The role of Co-60 gamma-ray irradiation on the interface states and series resistance in MIS structures**  
Tascioglu I., Tataroğlu A., Özbay A., Altindal Ş.  
RADIATION PHYSICS AND CHEMISTRY, cilt.79, ss.457-461, 2010 (SCI İndekslerine Giren Dergi)
- CCXIII. **The effect of frequency and illumination intensity on the main electrical characteristics of Al-TiW-Pd<sub>2</sub>Si/n-Si structures at room temperature**  
Uslu H., Safak Y., Tascioglu I., Altindal Ş.  
JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS, cilt.12, sa.2, ss.262-266, 2010 (SCI İndekslerine Giren Dergi)
- CCXIV. **The effects of surface states and series resistance on the performance of Au/SnO<sub>2</sub>/n-Si and Al/SnO<sub>2</sub>/p-Si (MIS) Schottky barrier diodes**  
Yildiz D. E. , Altindal Ş., Tekeli Z., Ozer M.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.13, sa.1, ss.34-40, 2010 (SCI İndekslerine Giren Dergi)
- CCXV. **On the temperature dependent profile of interface states and series resistance characteristics in (Ni/Au)/Al<sub>0.22</sub>Ga<sub>0.78</sub>N/AlN/GaN heterostructures**

- Demirezen S., Altındal Ş.  
PHYSICA B-CONDENSED MATTER, cilt.405, sa.4, ss.1130-1138, 2010 (SCI İndekslerine Giren Dergi)
- CCXVI. **Temperature dependent electrical and dielectric properties of Au/polyvinyl alcohol (Ni, Zn-doped)/n-Si Schottky diodes**  
Dokme İ., Altındal Ş., Tunc T., Uslu I.  
MICROELECTRONICS RELIABILITY, cilt.50, sa.1, ss.39-44, 2010 (SCI İndekslerine Giren Dergi)
- CCXVII. **Frequency and Temperature Dependence of Dielectric Properties of Au/Polyvinyl Alcohol (Co, Ni-Doped)/n-Si Schottky Diodes**  
TUNÇ T., Uslu I., DÖKME İ., ALTINDAL Ş., Uslu H.  
INTERNATIONAL JOURNAL OF POLYMERIC MATERIALS, cilt.59, sa.10, ss.739-756, 2010 (SCI İndekslerine Giren Dergi)
- CCXVIII. **Electrical characterization of current conduction in Au/TiO<sub>2</sub>/n-Si at wide temperature range**  
Altuntas H., Bengi A., AYDEMİR U., Asar T., Cetin S. Ş. , Kars İ., Altındal Ş., Ozcelik S.  
MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, cilt.12, sa.6, ss.224-232, 2009 (SCI İndekslerine Giren Dergi)
- CCXIX. **The effect of series resistance and surface states on current-voltage (I-V) characteristics of Au/n-GaAs/GaAs structures at wide temperature range**  
Bengi A., Mammadov T. S. , Ozcelik S., Altındal Ş.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.3, sa.11, ss.1155-1160, 2009 (SCI İndekslerine Giren Dergi)
- CCXX. **Analysis of surface states and series resistance in Au/n-Si Schottky diodes with insulator layer using current-voltage and admittance-voltage characteristics**  
Altındal Ş., Yucedag I., TATAROĞLU A.  
VACUUM, cilt.84, sa.3, ss.363-368, 2009 (SCI İndekslerine Giren Dergi)
- CCXXI. **The analysis of the series resistance and interface states of MIS Schottky diodes at high temperatures using I-V characteristics**  
TATAROĞLU A., Altındal Ş.  
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.484, ss.405-409, 2009 (SCI İndekslerine Giren Dergi)
- CCXXII. **Electrical Characteristics of Al/Polyindole Schottky Barrier Diodes. I. Temperature Dependence**  
Altındal Ş., SARI B., ÜNAL H. İ. , Yavas N.  
JOURNAL OF APPLIED POLYMER SCIENCE, cilt.113, sa.5, ss.2955-2961, 2009 (SCI İndekslerine Giren Dergi)
- CCXXIII. **A detailed study of current-voltage characteristics in Au/SiO<sub>2</sub>/n-GaAs in wide temperature range**  
Altuntas H., Altındal Ş., Shtrikman H., Ozcelik S.  
MICROELECTRONICS RELIABILITY, cilt.49, sa.8, ss.904-911, 2009 (SCI İndekslerine Giren Dergi)
- CCXXIV. **Electrical properties of Al/conducting polymer (P2ClAn)/p-Si/Al contacts**  
ÖZDEMİR A. F. , ALDEMİR D. A. , KÖKCE A., Altındal Ş.  
SYNTHETIC METALS, cilt.159, sa.14, ss.1427-1432, 2009 (SCI İndekslerine Giren Dergi)
- CCXXV. **Tunneling current via dislocations in Schottky diodes on AlInN/AlN/GaN heterostructures**  
Arslan E., ALTINDAL Ş., ÖZÇELİK S., ÖZBAY E.  
SEMICONDUCTOR SCIENCE AND TECHNOLOGY, cilt.24, sa.7, 2009 (SCI İndekslerine Giren Dergi)
- CCXXVI. **The distribution of barrier heights in MIS type Schottky diodes from current-voltage-temperature (I-V-T) measurements**  
TATAROĞLU A., ALTINDAL Ş.  
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.479, ss.893-897, 2009 (SCI İndekslerine Giren Dergi)
- CCXXVII. **The effects of the temperature on I-V and C-V characteristics of Al/P2ClAn(C<sub>2</sub>H<sub>5</sub>COOH)/p-Si/Al structure**  
Oezdemir A. F. , Kotan Z., ALDEMİR D. A. , Altındal Ş.  
EUROPEAN PHYSICAL JOURNAL-APPLIED PHYSICS, cilt.46, sa.2, 2009 (SCI İndekslerine Giren Dergi)
- CCXXVIII. **The effects of preparation temperature on the main electrical parameters of Al/TiO<sub>2</sub>/p-Si (MIS) structures by using sol-gel method**  
Pakma O., Serin N., Serin T., Altındal Ş.

- JOURNAL OF SOL-GEL SCIENCE AND TECHNOLOGY, cilt.50, sa.1, ss.28-34, 2009 (SCI İndekslerine Giren Dergi)
- CCXXXIX. **Gamma-ray irradiation effects on the interface states of MIS structures**  
TATAROĞLU A., Altındal Ş.
- SENSORS AND ACTUATORS A-PHYSICAL, cilt.151, sa.2, ss.168-172, 2009 (SCI İndekslerine Giren Dergi)
- CCXXX. **Characterization of series resistance in the Sn/p-InP Schottky barrier diodes using temperature dependent C-V,G/w and DLTS**  
Korucu D., Altındal Ş., Mammadov T. S. , Oezcelik S.
- OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.3, sa.3, ss.171-174, 2009 (SCI İndekslerine Giren Dergi)
- CCXXXI. **Electrical characteristics of Au/n-GaAs Schottky barrier diodes with and without SiO<sub>2</sub> insulator layer at room temperature**  
Altuntas H., Altındal Ş., Oezcelik S., Shtrikman H.
- VACUUM, cilt.83, sa.7, ss.1060-1065, 2009 (SCI İndekslerine Giren Dergi)
- CCXXXII. **Irradiation effects on the C-V and G/omega-V characteristics of Sn/p-Si (MS) structures**  
Karatas S., Tueruet A., Altındal Ş.
- RADIATION PHYSICS AND CHEMISTRY, cilt.78, sa.2, ss.130-134, 2009 (SCI İndekslerine Giren Dergi)
- CCXXXIII. **Origin of anomalous peak and negative capacitance in the forward bias C-V characteristics of Au/n-InP Schottky Barrier Diodes (SBDs)**  
Korucu D., Altındal Ş., Mammadov T. S. , Ozcelik S.
- JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS, cilt.11, sa.2, ss.192-196, 2009 (SCI İndekslerine Giren Dergi)
- CCXXXIV. **On the temperature dependent anomalous peak and negative capacitance in Au/n-InP Schottky barrier diodes**  
Korucu D., Altındal Ş., Mammadov T. S. , Oezcelik S.
- OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.3, sa.1, ss.56-59, 2009 (SCI İndekslerine Giren Dergi)
- CCXXXV. **Dislocation-governed current-transport mechanism in (Ni/Au)-AlGa<sub>N</sub>/AlN/GaN heterostructures**  
Arslan E., ALTINDAL Ş., Oezcelik S., ÖZBAY E.
- JOURNAL OF APPLIED PHYSICS, cilt.105, sa.2, 2009 (SCI İndekslerine Giren Dergi)
- CCXXXVI. **MBE-growth and characterization of In<sub>x</sub>Ga<sub>1-x</sub>As/GaAs (x=0.15) superlattice**  
Sarıkavak B., Oeztuerk M. K. , Altuntas H., Mammedov T. S. , Altındal Ş., Oezcelik S.
- REVISTA MEXICANA DE FISICA, cilt.54, sa.6, ss.416-421, 2008 (SCI İndekslerine Giren Dergi)
- CCXXXVII. **Temperature dependent behavior of Sn/p-InP Schottky barrier diodes**  
Korucu D., Altındal Ş., Mammadov T. S. , Oezcelik S.
- OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.2, sa.12, ss.766-769, 2008 (SCI İndekslerine Giren Dergi)
- CCXXXVIII. **Temperature dependence of electrical characteristics of Au/SiO<sub>2</sub>/n-GaAs (MOS) structures**  
Goekcen M., Altuntas H., Altındal Ş.
- OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.2, sa.12, ss.838-841, 2008 (SCI İndekslerine Giren Dergi)
- CCXXXIX. **The Double Gaussian Distribution of Inhomogeneous Barrier Heights in Al/GaN/p-GaAs (MIS) Schottky Diodes in Wide Temperature Range**  
Zeyrek S., Buelbuel M. M. , Altındal Ş., Baykul M. C. , Yuezzer H.
- BRAZILIAN JOURNAL OF PHYSICS, cilt.38, sa.4, ss.591-597, 2008 (SCI İndekslerine Giren Dergi)
- CCXL. **The profile of temperature and voltage dependent series resistance and the interface states in (Ni/Au)/Al<sub>0.3</sub>Ga<sub>0.7</sub>N/AlN/GaN heterostructures**  
Tekeli Z., Altındal Ş., Çakmak M., Ozcelik S., Ozbay E.
- MICROELECTRONIC ENGINEERING, cilt.85, ss.2316-2321, 2008 (SCI İndekslerine Giren Dergi)
- CCXLI. **Analysis of electrical characteristics of Au/SiO<sub>2</sub>/n-Si (MOS) capacitors using the high-low frequency capacitance and conductance methods**  
TATAROĞLU A., Altındal Ş.

- MICROELECTRONIC ENGINEERING, cilt.85, sa.11, ss.2256-2260, 2008 (SCI İndekslerine Giren Dergi)
- CCXLII. **Influence of frequency and bias voltage on dielectric properties and electrical conductivity of Al/TiO<sub>2</sub>/p-Si/p(+) (MOS) structures**  
Pakma O., Serin N., Serin T., Altındal Ş.  
JOURNAL OF PHYSICS D-APPLIED PHYSICS, cilt.41, sa.21, 2008 (SCI İndekslerine Giren Dergi)
- CCXLIII. **The influence of series resistance and interface states on intersecting behavior of I-V characteristics of Al/TiO<sub>2</sub>/p-Si (MIS) structures at low temperatures**  
Pakma O., Serin N., Serin T., Altındal Ş.  
SEMICONDUCTOR SCIENCE AND TECHNOLOGY, cilt.23, sa.10, 2008 (SCI İndekslerine Giren Dergi)
- CCXLIV. **Analysis of temperature dependent electrical characteristics of Au/n-GaAs/GaAs structures in a wide temperature range**  
Bengi A., Altındal Ş., Ozelik S., Agaliyeva S. T., Mammadov T. S.  
VACUUM, cilt.83, sa.2, ss.276-281, 2008 (SCI İndekslerine Giren Dergi)
- CCXLV. **Frequency and gate voltage effects on the dielectric properties of Au/SiO<sub>2</sub>/n-Si structures**  
Dokme İ., ALTINDAL Ş., Gokcen M.  
MICROELECTRONIC ENGINEERING, cilt.85, sa.9, ss.1910-1914, 2008 (SCI İndekslerine Giren Dergi)
- CCXLVI. **The frequency dependent electrical characteristics of Sn/p-InP Schottky barrier diodes (SBDs)**  
Korucu D., Altındal Ş., Mammadov T. S., Oezcelik S.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.2, sa.9, ss.525-529, 2008 (SCI İndekslerine Giren Dergi)
- CCXLVII. **Study on the frequency dependence of electrical and dielectric characteristics of Au/SnO<sub>2</sub>/n-Si (MIS) structures**  
TATAROĞLU A., Altındal Ş.  
MICROELECTRONIC ENGINEERING, cilt.85, sa.9, ss.1866-1871, 2008 (SCI İndekslerine Giren Dergi)
- CCXLVIII. **Dielectric properties and ac electrical conductivity studies of MIS type Schottky diodes at high temperatures**  
TATAROĞLU A., Yuecedag I., Altındal Ş.  
MICROELECTRONIC ENGINEERING, cilt.85, sa.7, ss.1518-1523, 2008 (SCI İndekslerine Giren Dergi)
- CCXLIX. **On the energy distribution of interface states and their relaxation time and capture cross section profiles in Al/SiO<sub>2</sub>/P-Si (MIS) Schottky diodes**  
Altındal Ş., Kanbur H., Yuecedag I., TATAROĞLU A.  
MICROELECTRONIC ENGINEERING, cilt.85, sa.7, ss.1495-1501, 2008 (SCI İndekslerine Giren Dergi)
- CCL. **The double Gaussian distribution of barrier heights in Al/TiO<sub>2</sub>/p-Si (metal-insulator-semiconductor) structures at low temperatures**  
Pakma O., Serin N., Serin T., Altındal Ş.  
JOURNAL OF APPLIED PHYSICS, cilt.104, sa.1, 2008 (SCI İndekslerine Giren Dergi)
- CCLI. **Characterization of interface states at Au/SnO<sub>2</sub>/n-Si (MOS) structures**  
TATAROĞLU A., Altındal Ş.  
VACUUM, cilt.82, sa.11, ss.1203-1207, 2008 (SCI İndekslerine Giren Dergi)
- CCLII. **The temperature profile and bias dependent series resistance of Au/Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>/SiO<sub>2</sub>/n-Si (MFIS) structures**  
Altındal Ş., Parlaktuerk F., TATAROĞLU A., PARLAK M., Sarmasov S. N., Agasiev A. A.  
VACUUM, cilt.82, sa.11, ss.1246-1250, 2008 (SCI İndekslerine Giren Dergi)
- CCLIII. **Gaussian distribution of inhomogeneous barrier height in Al/SiO<sub>2</sub>/p-Si Schottky diodes**  
Yildiz D. E., Altındal Ş., Kanbur H.  
JOURNAL OF APPLIED PHYSICS, cilt.103, sa.12, 2008 (SCI İndekslerine Giren Dergi)
- CCLIV. **Effects of gamma-ray irradiation on the C-V and G/omega-V characteristics of Al/SiO<sub>2</sub>/p-Si (MIS) structures**  
Dokme İ., DURMUŞ P., ALTINDAL Ş.  
NUCLEAR INSTRUMENTS & METHODS IN PHYSICS RESEARCH SECTION B-BEAM INTERACTIONS WITH MATERIALS AND ATOMS, cilt.266, sa.5, ss.791-796, 2008 (SCI İndekslerine Giren Dergi)

- CCLV. **The interface states analysis of the MIS structure as a function of frequency**  
TATAROĞLU A., Altındal Ş.  
MICROELECTRONIC ENGINEERING, cilt.85, sa.3, ss.542-547, 2008 (SCI İndekslerine Giren Dergi)
- CCLVI. **The distribution of the barrier height in Al-TiW-Pd<sub>2</sub>Si/n-Si Schottky diodes from I-V-T measurements**  
Dokme İ., ALTINDAL Ş., Afandiyeva I. M.  
SEMICONDUCTOR SCIENCE AND TECHNOLOGY, cilt.23, sa.3, 2008 (SCI İndekslerine Giren Dergi)
- CCLVII. **Effects of illumination and Co-60 gamma-ray irradiation on the electrical characteristics of porous silicon solar cells**  
Tuezuen O., Altındal Ş., Oktik S.  
RENEWABLE ENERGY, cilt.33, sa.2, ss.286-292, 2008 (SCI İndekslerine Giren Dergi)
- CCLVIII. **Frequency and voltage effects on the dielectric properties and electrical conductivity of Al-TiW-Pd<sub>2</sub>Si/n-Si structures**  
Afandiyeva I. M., Doekme İ., Altındal Ş., Buelbuel M. M., TATAROĞLU A.  
MICROELECTRONIC ENGINEERING, cilt.85, sa.2, ss.247-252, 2008 (SCI İndekslerine Giren Dergi)
- CCLIX. **On the temperature dependence of series resistance and interface states in Al/SiO<sub>2</sub>/p-Si (MIS) Schottky diodes**  
Yildiz D. E., Altındal Ş.  
MICROELECTRONIC ENGINEERING, cilt.85, sa.2, ss.289-294, 2008 (SCI İndekslerine Giren Dergi)
- CCLX. **The frequency and voltage dependent electrical characteristics of Al-TiW-Pd<sub>2</sub>Si/n-Si structure using I-V, C-V and G/omega-V measurements**  
Afandiyeva I. M., Doekme İ., Altındal Ş., Abdullayeva L. K., Askerov S. G.  
MICROELECTRONIC ENGINEERING, cilt.85, sa.2, ss.365-370, 2008 (SCI İndekslerine Giren Dergi)
- CCLXI. **On the profile of frequency dependent series resistance and surface states in Au/Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>/SiO<sub>2</sub>/n-Si(MFIS) structures**  
Parlaktuerk F., Altındal Ş., TATAROĞLU A., PARLAK M., Agasiev A.  
MICROELECTRONIC ENGINEERING, cilt.85, sa.1, ss.81-88, 2008 (SCI İndekslerine Giren Dergi)
- CCLXII. **Analysis of interface states and series resistance of MIS Schottky diodes using the current-voltage (I-V) characteristics**  
TATAROĞLU A., Altındal Ş.  
MICROELECTRONIC ENGINEERING, cilt.85, sa.1, ss.233-237, 2008 (SCI İndekslerine Giren Dergi)
- CCLXIII. **The effect of Co-60 (gamma-ray) irradiation Au/SnO<sub>2</sub>/n-Si on the electrical characteristics of (MIS) structures**  
Goekcen M., TATAROĞLU A., Altındal Ş., Buelbuel M. M.  
RADIATION PHYSICS AND CHEMISTRY, cilt.77, sa.1, ss.74-78, 2008 (SCI İndekslerine Giren Dergi)
- CCLXIV. **The barrier height distribution in identically prepared Al/p-Si Schottky diodes with the native interfacial insulator layer (SiO<sub>2</sub>)**  
Altındal Ş., Kanbur H., TATAROĞLU A., Buelbuel M. M.  
PHYSICA B-CONDENSED MATTER, cilt.399, sa.2, ss.146-154, 2007 (SCI İndekslerine Giren Dergi)
- CCLXV. **Irradiation effect on dielectric properties and electrical conductivity of Au/SiO<sub>2</sub>/n-Si (MOS) structures**  
TATAROĞLU A., Altındal Ş., Boeluekdemir M. H., Tanir G.  
Nuclear Instruments and Methods in Physics Research, Section B: Beam Interactions with Materials and Atoms, cilt.264, sa.1, ss.73-78, 2007 (SCI Expanded İndekslerine Giren Dergi)
- CCLXVI. **Analysis of interface states and series resistance at MIS structure irradiated under Co-60 gamma-rays**  
TATAROĞLU A., Altındal Ş.  
NUCLEAR INSTRUMENTS & METHODS IN PHYSICS RESEARCH SECTION A-ACCELERATORS SPECTROMETERS DETECTORS AND ASSOCIATED EQUIPMENT, cilt.580, sa.3, ss.1588-1593, 2007 (SCI İndekslerine Giren Dergi)
- CCLXVII. **The behavior of the I-V-T characteristics of inhomogeneous (Ni/Au)-Al<sub>0.3</sub>Ga<sub>0.7</sub>N/AlN/GaN heterostructures at high temperatures**



- Tekeli Z., Altindal Ş., ÇAKMAK M., Oezaelik S., Caliskan D., Oezbay E.  
 JOURNAL OF APPLIED PHYSICS, cilt.102, sa.5, 2007 (SCI İndekslerine Giren Dergi)
- CCLXVIII. **Current-voltage characteristics of Al/Rhodamine-101/n-GaAs and Cu/Rhodamine-101/n-GaAs rectifier contacts**  
 Vural O., Yildirim N., Altindal Ş., Tueruet A.  
 SYNTHETIC METALS, cilt.157, ss.679-683, 2007 (SCI İndekslerine Giren Dergi)
- CCLXIX. **Temperature dependence of characteristic parameters of the Au/SnO<sub>2</sub>/n-Si (MIS) Schottky diodes**  
 Ozer M., Yildiz D. E., Altindal Ş., Bulbul M. M.  
 SOLID-STATE ELECTRONICS, cilt.51, sa.6, ss.941-949, 2007 (SCI İndekslerine Giren Dergi)
- CCLXX. **Gaussian distribution of inhomogeneous barrier height in Al<sub>0.24</sub>Ga<sub>0.76</sub>As/GaAs structures**  
 Bengi A., Altindal Ş., Ozcelik S., Mammadov T. S.  
 PHYSICA B-CONDENSED MATTER, cilt.396, ss.22-28, 2007 (SCI İndekslerine Giren Dergi)
- CCLXXI. **Electrical transport characteristics of Sn/p-Si schottky contacts revealed from I-V-T and C-V-T measurements**  
 Karatas S., Altindal Ş., Turut A., Cakar M.  
 PHYSICA B-CONDENSED MATTER, cilt.392, ss.43-50, 2007 (SCI İndekslerine Giren Dergi)
- CCLXXII. **On the profile of frequency and voltage dependent interface states and series resistance in MIS structures**  
 Dokme İ., Altindal Ş.  
 PHYSICA B-CONDENSED MATTER, cilt.393, ss.328-335, 2007 (SCI İndekslerine Giren Dergi)
- CCLXXIII. **Current conduction mechanism in Al/p-Si Schottky barrier diodes with native insulator layer at low temperatures**  
 Altindal Ş., Kanbur H., Yildiz D. E., Parlak M.  
 APPLIED SURFACE SCIENCE, cilt.253, sa.11, ss.5056-5061, 2007 (SCI İndekslerine Giren Dergi)
- CCLXXIV. **The C-V-f and G/omega-V-f characteristics of Au/SiO<sub>2</sub>/n-Si capacitors**  
 Dokme İ., Altindal Ş.  
 PHYSICA B-CONDENSED MATTER, cilt.391, sa.1, ss.59-64, 2007 (SCI İndekslerine Giren Dergi)
- CCLXXV. **The effects of frequency and gamma-irradiation on the dielectric properties of MIS type Schottky diodes**  
 TATAROĞLU A., Altindal Ş.  
 NUCLEAR INSTRUMENTS & METHODS IN PHYSICS RESEARCH SECTION B-BEAM INTERACTIONS WITH MATERIALS AND ATOMS, cilt.254, sa.1, ss.113-117, 2007 (SCI İndekslerine Giren Dergi)
- CCLXXVI. **Effects of beta-ray irradiation on the C-V and G/omega-V characteristics of Au/SiO<sub>2</sub>/n-Si (MOS) structures**  
 TATAROĞLU A., Bolukdemir M. H., Tanir G., Altindal Ş., Bulbul M. M.  
 Nuclear Instruments and Methods in Physics Research, Section B: Beam Interactions with Materials and Atoms, cilt.254, sa.2, ss.273-277, 2007 (SCI Expanded İndekslerine Giren Dergi)
- CCLXXVII. **On the profile of frequency dependent series resistance and dielectric constant in MIS structure**  
 Yuicedag I., Altindal Ş., TATAROĞLU A.  
 MICROELECTRONIC ENGINEERING, cilt.84, sa.1, ss.180-186, 2007 (SCI İndekslerine Giren Dergi)
- :CLXXVIII. **Co-60 gamma irradiation effects on the current-voltage (I-V) characteristics of Al/SiO<sub>2</sub>/P-Si (MIS) Schottky diodes**  
 TATAROĞLU A., Altindal Ş., Bulbul M. M.  
 NUCLEAR INSTRUMENTS & METHODS IN PHYSICS RESEARCH SECTION A-ACCELERATORS SPECTROMETERS DETECTORS AND ASSOCIATED EQUIPMENT, cilt.568, sa.2, ss.863-868, 2006 (SCI İndekslerine Giren Dergi)
- CCLXXIX. **Electrical characteristics of Co-60 gamma-ray irradiated MIS Schottky diodes**  
 TATAROĞLU A., Altindal Ş.  
 NUCLEAR INSTRUMENTS & METHODS IN PHYSICS RESEARCH SECTION B-BEAM INTERACTIONS WITH MATERIALS AND ATOMS, cilt.252, sa.2, ss.257-262, 2006 (SCI İndekslerine Giren Dergi)
- CCLXXX. **Frequency and voltage dependent surface states and series resistance of novel Si solar cells**  
 Tuzun O., Altindal Ş., Oktik S.

- MATERIALS SCIENCE AND ENGINEERING B-SOLID STATE MATERIALS FOR ADVANCED TECHNOLOGY, cilt.134, ss.291-295, 2006 (SCI İndekslerine Giren Dergi)
- CCLXXXI. **The barrier height inhomogeneity in Al/p-Si Schottky barrier diodes with native insulator layer**  
Dokme İ., Altındal Ş., Bulbul M. M.  
APPLIED SURFACE SCIENCE, cilt.252, sa.22, ss.7749-7754, 2006 (SCI İndekslerine Giren Dergi)
- CCLXXXII. **On the intersecting behaviour of experimental forward bias current-voltage (I-V) characteristics of Al/SiO<sub>2</sub>/p-Si (MIS) Schottky diodes at low temperatures**  
Dokme İ., Altındal Ş.  
SEMICONDUCTOR SCIENCE AND TECHNOLOGY, cilt.21, sa.8, ss.1053-1058, 2006 (SCI İndekslerine Giren Dergi)
- CLXXXIII. **Electrical characterization of novel Si solar cells**  
Tuzun O., Oktik S., Altındal Ş., Mammadov T. S.  
THIN SOLID FILMS, cilt.511, ss.258-264, 2006 (SCI İndekslerine Giren Dergi)
- CLXXXIV. **Characterization of current-voltage (I-V) and capacitance-voltage-frequency (C-V-f) features of Al/SiO<sub>2</sub>/p-Si (MIS) Schottky diodes**  
TATAROĞLU A., Altındal Ş.  
MICROELECTRONIC ENGINEERING, cilt.83, sa.3, ss.582-588, 2006 (SCI İndekslerine Giren Dergi)
- CCLXXXV. **The role of the interface insulator layer and interface states on the current-transport mechanism of Schottky diodes in wide temperature range**  
Altındal Ş., Dokme İ., Bulbul M., Yalcin N., Serin T.  
MICROELECTRONIC ENGINEERING, cilt.83, sa.3, ss.499-505, 2006 (SCI İndekslerine Giren Dergi)
- CLXXXVI. **On the profile of temperature dependent series resistance in Al/Si<sub>3</sub>N<sub>4</sub>/p-Si (MIS) Schottky diodes**  
Bulbul M., Zeyrek S., Altındal Ş., Yuzer H.  
MICROELECTRONIC ENGINEERING, cilt.83, sa.3, ss.577-581, 2006 (SCI İndekslerine Giren Dergi)
- CLXXXVII. **Current transport mechanism in Al/Si<sub>3</sub>N<sub>4</sub>/p-Si (MIS) Schottky barrier diodes at low temperatures**  
Zeyrek S., Altındal Ş., Yuzer H., Bulbul M.  
APPLIED SURFACE SCIENCE, cilt.252, sa.8, ss.2999-3010, 2006 (SCI İndekslerine Giren Dergi)
- LXXXVIII. **The effect of interface states, excess capacitance and series resistance in the Al/SiO<sub>2</sub>/P-Si Schottky diodes**  
Kanbur H., Altındal Ş., TATAROĞLU A.  
APPLIED SURFACE SCIENCE, cilt.252, sa.5, ss.1732-1738, 2005 (SCI İndekslerine Giren Dergi)
- CLXXXIX. **Effects of Co-60 gamma-ray irradiation on the electrical characteristics of Au/n-GaAs (MS) structures**  
Karatas S., Turut A., Altındal Ş.  
NUCLEAR INSTRUMENTS & METHODS IN PHYSICS RESEARCH SECTION A-ACCELERATORS SPECTROMETERS DETECTORS AND ASSOCIATED EQUIPMENT, cilt.555, ss.260-265, 2005 (SCI İndekslerine Giren Dergi)
- CCXC. **Analysis of I-V characteristics on Au/n-type GaAs Schottky structures in wide temperature range**  
Karatas S., Altındal Ş.  
MATERIALS SCIENCE AND ENGINEERING B-SOLID STATE MATERIALS FOR ADVANCED TECHNOLOGY, cilt.122, sa.2, ss.133-139, 2005 (SCI İndekslerine Giren Dergi)
- CCXCI. **Temperature and frequency dependent electrical and dielectric properties of Al/SiO<sub>2</sub>/p-Si (MOS) structure**  
TATAROĞLU A., Altındal Ş., Bulbul M.  
MICROELECTRONIC ENGINEERING, cilt.81, sa.1, ss.140-149, 2005 (SCI İndekslerine Giren Dergi)
- CCXCII. **Temperature dependence of barrier heights of Au/n-type GaAs Schottky diodes**  
Karatas S., Altındal Ş.  
SOLID-STATE ELECTRONICS, cilt.49, sa.6, ss.1052-1054, 2005 (SCI İndekslerine Giren Dergi)
- CCXCIII. **Current transport in Zn/p-Si(100) Schottky barrier diodes at high temperatures**  
Karatas S., Altındal Ş., Cakar M.  
PHYSICA B-CONDENSED MATTER, cilt.357, ss.386-397, 2005 (SCI İndekslerine Giren Dergi)
- CCXCIV. **Density of interface states, excess capacitance and series resistance in the metal-insulator-semiconductor (MIS) solar cells**

- Altindal Ş., TATAROĞLU A., Dokme İ.  
SOLAR ENERGY MATERIALS AND SOLAR CELLS, cilt.85, sa.3, ss.345-358, 2005 (SCI İndekslerine Giren Dergi)
- CCXCV. **Effect of series resistance on the performance of silicon Schottky diode in the presence of tin oxide layer**  
Tugluoglu N., Karadeniz S., Altindal Ş.  
APPLIED SURFACE SCIENCE, cilt.239, ss.481-489, 2005 (SCI İndekslerine Giren Dergi)
- CCXCVI. **Dielectric properties in Au/SnO<sub>2</sub>/n-Si (MOS) structures irradiated under Co-60-gamma rays**  
Tugluoglu N., Altindal Ş., TATAROĞLU A., Karadeniz S.  
MICROELECTRONICS JOURNAL, cilt.35, sa.9, ss.731-738, 2004 (SCI İndekslerine Giren Dergi)
- CCXCVII. **Au/SnO<sub>2</sub>/n-Si (MOS) structures response to radiation and frequency**  
TATAROĞLU A., Altindal Ş., Karadeniz S., Tugluoglu N.  
MICROELECTRONICS JOURNAL, cilt.34, sa.11, ss.1043-1049, 2003 (SCI İndekslerine Giren Dergi)
- CCXCVIII. **The role of interface states and series resistance on the I-V and C-V characteristics in Al/SnO<sub>2</sub>/p-Si Schottky diodes**  
Altindal Ş., Karadeniz S., Tugluoglu N., TATAROĞLU A.  
SOLID-STATE ELECTRONICS, cilt.47, sa.10, ss.1847-1854, 2003 (SCI İndekslerine Giren Dergi)
- CCXCIX. **Temperature dependence of characteristic parameters of the H-terminated Sn/p-Si(100) Schottky contacts**  
Karatas S., Altindal Ş., Turut A., Ozmen A.  
APPLIED SURFACE SCIENCE, cilt.217, ss.250-260, 2003 (SCI İndekslerine Giren Dergi)
- CCC. **Coherent infrared image converter based on GaAs and BSO crystals**  
Salamov B., Kurt H., Lebedeva N., Altindal Ş., Ozer M.  
IMAGING SCIENCE JOURNAL, cilt.49, sa.4, ss.197-203, 2001 (SCI İndekslerine Giren Dergi)
- CCCI. **The concentration of currents on the artificial surface inhomogeneities of semiconducting cathodes in ionization cells**  
Salamov B., Ozer M., Kasap M., Altindal Ş.  
JOURNAL OF PHYSICS D-APPLIED PHYSICS, cilt.32, sa.6, ss.682-687, 1999 (SCI İndekslerine Giren Dergi)
- CCCII. **Characteristic features of an ionization system with semiconducting cathode**  
Salamov B., Altindal Ş., Ozer M., Colakoglu K., BULUR E.  
EUROPEAN PHYSICAL JOURNAL-APPLIED PHYSICS, cilt.2, sa.3, ss.267-273, 1998 (SCI İndekslerine Giren Dergi)
- CCCIII. **Complex-radical cyclopolymerization of allyl a-(N-maleimido)acetate with styrene and maleic anhydride**  
Rzaev Z., Salamova U., Altindal Ş.  
MACROMOLECULAR CHEMISTRY AND PHYSICS, cilt.198, sa.8, ss.2475-2487, 1997 (SCI İndekslerine Giren Dergi)
- CCCIV. **Photoelectrical properties of semiconductor in contact with gas discharge plasma**  
Lebedeva N., Orbukh V., Salamov B., Ozer M., Colakoglu K., Altindal Ş.  
JOURNAL DE PHYSIQUE III, cilt.7, sa.5, ss.1039-1044, 1997 (SCI İndekslerine Giren Dergi)
- CCCV. **A stable discharge glow in gas discharge system with semiconducting cathode**  
Salamov B., Colakoglu K., Altindal Ş., Ozer M.  
JOURNAL DE PHYSIQUE III, cilt.7, sa.4, ss.927-936, 1997 (SCI İndekslerine Giren Dergi)
- CCCVI. **The rapid visualization of resistivity inhomogeneities in high-resistivity semiconductor films**  
Salamov B., Civi M., Altindal Ş., Kasap M., BULUR E.  
JOURNAL OF INFORMATION RECORDING, cilt.23, sa.5, ss.437-445, 1997 (SCI İndekslerine Giren Dergi)
- CCCVII. **Influence of gas medium on the sensitivity of an ionization type semiconductor photographic system**  
Salamov B., Colakoglu K., Altindal Ş.  
IMAGING SCIENCE JOURNAL, cilt.45, sa.2, ss.65-68, 1997 (SCI İndekslerine Giren Dergi)
- CCCVIII. **Effect of inorganic salts on the main parameters of the dilute aqueous poly(vinylpyrrolidone) solutions**  
Salamova U., Rzaev Z., Altindal Ş., Masimov A.  
POLYMER, cilt.37, sa.12, ss.2415-2421, 1996 (SCI İndekslerine Giren Dergi)
- CCCIX. **Enhancement of the sensitivity of an ionization type semiconductor photographic system**

- Salamov B., Colakoglu K., Altindal Ş., Ozer M.  
JOURNAL OF PHOTOGRAPHIC SCIENCE, cilt.44, sa.4, ss.110-115, 1996 (SCI İndekslerine Giren Dergi)
- CCCX. **RECORDING THE RESISTANCE INHOMOGENEITY IN HIGH-RESISTIVITY SEMICONDUCTORS PLATES**  
SALAMOV B., COLAKOĞLU K., ALTINDAL Ş.  
INFRARED PHYSICS & TECHNOLOGY, cilt.36, sa.3, ss.661-668, 1995 (SCI İndekslerine Giren Dergi)
- CCCXI. **TEMPERATURE-DEPENDENT ELECTRICAL CHARACTERISTICS OF AL-SIOX-PSI SOLAR-CELLS**  
OZDEMİR S., ALTINDAL Ş.  
SOLAR ENERGY MATERIALS AND SOLAR CELLS, cilt.32, sa.2, ss.115-127, 1994 (SCI İndekslerine Giren Dergi)

## **Diğer Dergilerde Yayınlanan Makaleler**

- I. **On the profile of temperature dependent main electrical parameters in Al/P3HT/p-Si (MPS) structures at low temperatures**  
YÜKSELTÜRK E., ZEYREK S., ALTINDAL Ş., BÜLBÜL M. M.  
Materials Today: Proceedings, cilt.18, ss.1852-1860, 2019 (Diğer Kurumların Hakemli Dergileri)
- II. **The Investigation of Frequency and Voltage Dependence of Electrical Characteristics in Al/P3HT/p-Si (MPS) Structures**  
YÜKSELTÜRK E., ÇOTUK M., ZEYREK S., ALTINDAL Ş., BÜLBÜL M. M.  
Materials Today: Proceedings, cilt.18, ss.1842-1851, 2019 (Diğer Kurumların Hakemli Dergileri)
- III. **Self-assembled patches in PtSi/n-Si (111) diodes**  
Afandiyeva I. M. , Altindal Ş., Abdullayeva L. K. , Bayramova A. I.  
JOURNAL OF SEMICONDUCTORS, cilt.39, sa.5, 2018 (ESCI İndekslerine Giren Dergi)
- IV. **The Effect of Modified PVA Interfacial Layer Doped by Zn Nanoparticles on the Electrical Parameters of Au/N-4H Sic (MS) Structures**  
AlDharob M. H. , KÖKCE A., Lapa H. E. , ÖZDEMİR A. F. , ALTINDAL Ş.  
Polymer Sciences, cilt.4, sa.1, 2018 (Diğer Kurumların Hakemli Dergileri)
- V. **Analysis of Barrier Height and Carrier Concentration of MOS Capacitor Using C f and G f Measurements**  
Parlaktürk F., Agasiev A., TATAROĞLU A., ALTINDAL Ş.  
Gazi University Journal of Science, cilt.27, ss.909-915, 2014 (Diğer Kurumların Hakemli Dergileri)
- VI. **Dielectric Permittivity AC Conductivity and Electric Modulus Properties of Metal Ferroelectric Semiconductor MFS Structures**  
Parlaktürk F., Agasiev A., TATAROĞLU A., ALTINDAL Ş.  
Gazi University Journal of Science, cilt.26, ss.501-508, 2013 (Diğer Kurumların Hakemli Dergileri)
- VII. **Temperature Dependence Electrical Characteristics of n-GaAs Structure Grown by MBE**  
Kınacı B., Asar T., Özen Y., Altindal Ş., Mammadov T., Özçelik S.  
Azerbaijan Journal of Physics, Fizika, cilt.16, sa.2, ss.335-338, 2010 (Diğer Kurumların Hakemli Dergileri)
- VIII. **A comparative of energy density distribution of surface states profiles with 50 and 826 Å insulator layer in Al SiO2 p Si**  
ALTINDAL Ş., KAYA A., SÖNMEZ Z., ŞAFAK ASAR Y.  
Azerbaijan Journal of Physics, Fizika, (ISSN 1028-8546), cilt.16, sa.2, ss.356-358, 2010 (Diğer Kurumların Hakemli Dergileri)
- IX. **Frequency Dependent Electrical Characteristics of Metal Ferroelectric Semiconductor Au SrTiO3 n Si Structures**  
AYDEMİR U., ŞAFAK ASAR Y., ALTINDAL Ş., AGASİYEV A. A.  
Journal of Optoelectronics and Advanced Materials - Symposia, cilt.1, sa.3, ss.258-261, 2009 (Diğer Kurumların Hakemli Dergileri)
- X. **On the Frequency and Voltage Dependent Interface States and Series Resistance in Au SrTiO3 n Si Structures**  
AYDEMİR U., ŞAFAK ASAR Y., MAMMADOV T. S. , ALTINDAL Ş.

Balkan Physics Letters, cilt.15, sa.1, ss.151050, 2009 (Diğer Kurumların Hakemli Dergileri)

- XI. **Temperature Dependent Electrical Characteristics of Metal Ferroelectric Semiconductor Au SrTiO<sub>3</sub> n Si Structures**  
ŞAFAK ASAR Y., AYDEMİR U., ALTINDAL Ş., MAMMADOV T. S., TATAROĞLU A.  
Journal of Optoelectronics and Advanced Materials - Symposia, cilt.1, sa.3, ss.266-269, 2009 (Diğer Kurumların Hakemli Dergileri)
- XII. **The Barrier Height Distribution in Metal Ferroelectric Semiconductor Au SrTiO<sub>3</sub> n Si Structures**  
ŞAFAK ASAR Y., AYDEMİR U., ALTINDAL Ş., MAMMADOV T.  
Balkan Physics Letters, cilt.15, sa.1, ss.151056, 2009 (Diğer Kurumların Hakemli Dergileri)
- XIII. **Current Voltage I V and Capacitance Voltage C V Characteristics of Au Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> SnO<sub>2</sub> Structures**  
Parlaktürk F., Agasiev A., TATAROĞLU A., ALTINDAL Ş.  
Gazi University Journal of Science, cilt.20, ss.97-102, 2007 (Diğer Kurumların Hakemli Dergileri)
- XIV. **Frequency and Temperature Dependent Interface States and Series Resistance of Au CdTe Schottky Diodes**  
MAMMADOV T. S., KANBUR ÇAVUŞ H., ŞAFAK ASAR Y., ALTINDAL Ş., ACAR S., AKHMEDZADE N. D.  
Azerbaijan Journal of Physics, Fizika, cilt.13, sa.4, ss.219-223, 2007 (Diğer Kurumların Hakemli Dergileri)

### **Hakemli Kongre / Sempozyum Bildiri Kitaplarında Yer Alan Yayınlar**

- I. **Comprehensive Investigation on Dielectric Properties of Al/CdSPVA/p-Si Structures at 5 kHz-5 MHz**  
AzizianKalandaragh Y., YÜCEDAĞ İ., ERSÖZ DEMİR G., ALTINDAL Ş.  
6th International Conference on Materials Science and Nanotechnology For Next Generation (MSNG2019), 16 - 18 Ekim 2019
- II. **Investigation of Gamma Irradiation Effects on The Current-Voltage Characteristics of Au/n-Si/Ag Schottky Diodes (SDs)**  
KAYMAZ A., ALTINDAL Ş., TECİMER H.  
6th International Conference on Materials Science and Nanotechnology For Next Generation (MSNG-2019), Niğde, Türkiye, 16 - 18 Ekim 2019, ss.416-419
- III. **Temperature Dependent Barrier Height, Ideality Factor, Series Resistance of the Al/Al<sub>2</sub>O<sub>3</sub>/p-Si (MIS) Diodes Using Cheung's Functions in Temperature Range of 200-320 K**  
KOŞAL M., MARIL E., ALTINDAL Ş.  
1st International Conference on Optoelectronics, Applied Optics and Microelectronics, ERDEBİL, İran, 17 - 19 Ağustos 2019
- IV. **A Comparison Electrical Parameters of Au/n-Si (MS) and Au/(ITO-PVP)/n-Si (MPS) Structures Obtained from the Forward Bias (IV) and Reverse Bias (CV) Characteristics**  
SEVGİLİ Ö., Azizian Kalandaragh Y., ALTINDAL Ş.  
1st International Conference on Optoelectronics, Applied Optics and Microelectronics, 17 - 19 Ağustos 2019
- V. **Temperature Dependent Current-Transport Mechanisms (CTMs) in the Al/Al<sub>2</sub>O<sub>3</sub>/p-Si (MIS) Diodes (SDs) Using Current-Voltage-Temperature (I-V-T) Characteristics in the Temperature Range of 200-320 K**  
MARIL E., KOŞAL M., ALTINDAL Ş.  
1ST INTERNATIONAL CONFERENCE ON OPTOELECTRONICS, APLIED OPTİCS AND MICROELECTRONICS, ERDEBİL, İran, 17 - 19 Ağustos 2019
- VI. **CAPACITANCE-VOLTAGE (C-V) AND CONDUCTANCE-VOLTAGE (G/ħ-V) CHARACTERISTICS BEFORE AND AFTER IRRADIATION IN Au/n-Si/AgSCHOTTKY BARRIER DIODES (SBDs)**  
DURMUŞ P., ALTINDAL Ş., KAYMAZ A.  
International Natural Science, Engineering and Materials Technology Conference, İstanbul, Türkiye, 9 - 10 Eylül 2019, ss.9-14
- VII. **THE INVESTIGATION OF EFFECTS OF (NANOCARBON DOPED-PVP) POLYMER INTERFACIAL LAYER ON THE MAIN ELECTRICAL PARAMETERS AND CONDUCTIVITY**

DÖKME İ., ALTINDAL Ş.

International Natural Science, Engineering and Materials Technology Conference Sep 9-10, 2019, İstanbul / TURKEY, Türkiye, 9 - 10 Eylül 2019

- VIII. **The Investigation of Temperature Dependent Current – Transfer Mechanisms of Au/PVA/n-GaAs**  
EVCİN E., TECİMER H., ALTINDAL Ş., TECİMER H.  
MSNG 2019, 16 - 18 Ekim 2019
- IX. **Utilization of Al<sub>2</sub>O<sub>3</sub>/PVP nanocomposite as an interfacial layer for schottky structures**  
Akin B., Pirgholi-Givi G., Farazin J., Azizian-Kalandaragh Y., ALTINDAL Ş.  
13th International Congress on Artificial Materials for Novel Wave Phenomena, Metamaterials 2019, Rome, İtalya, 16 - 21 Eylül 2019
- X. **Morphological and structural properties of metamaterial based on ITO/Sapphire/ZnS/Al superlattice**  
Akin B., ALTINDAL Ş., Farazin J., Pirgholi-Givi G., Azizian-Kalandaragh Y.  
21st International Conference on Electromagnetics in Advanced Applications, ICEAA 2019, Granada, İspanya, 9 - 13 Eylül 2019, ss.816-819
- XI. **On the profile of temperature dependent main electrical parameters in Al/P3HT/p-Si (MPS) structures at low temperatures**  
Yukselturk E., Cotuk M., Bulbul M. M. , Altindal Ş., Zeyrek S.  
International Congress on Semiconductor Materials and Devices (ICSMD), Konya, Türkiye, 17 - 19 Ağustos 2017, cilt.18, ss.1852-1860
- XII. **TEMPERATURE DEPENDENCED CONDUCTIVITY OF PtSi/n-Si SCHOTTKY DIODES WITH SELF-ASSEMBLED PATCHES**  
Afandiyeva I. M. , Altindal Ş.  
International Conference on Modern Trends in Physics, Baku, Azerbaycan, 1 - 03 Mayıs 2019, ss.80-83
- XIII. **The Investigation of Frequency and Voltage Dependence of Electrical Characteristics in Al/P3HT/p-Si (MPS) Structures**  
Yukselturk E., Cotuk M., Zeyrek S., Altindal Ş., Bulbul M. M.  
International Congress on Semiconductor Materials and Devices (ICSMD), Konya, Türkiye, 17 - 19 Ağustos 2017, cilt.18, ss.1842-1851
- XIV. **Temperature and Frequency Dependence Electrical Characteristics of Au/n-Si (SBD) With A Thin PPy Interfacial Layer In The Wide Range Of Applied Bias Voltage**  
MARIL E., ALTINDAL Ş.  
MSNG 2018, Nevşehir, Türkiye, 25 - 26 Ekim 2018
- XV. **Study of frequency dispersion effect on admittance characteristics of Au/ZnFe<sub>2</sub>O<sub>4</sub>-PVA /n-Si structures**  
TAŞÇIOĞLU İ., Kalandaragh Y. A. , Badali Y., ALTINDAL Ş.  
International Materials Science and Nanotechnology For Next Generation conference (MSNG2018), 4 - 06 Ekim 2018
- XVI. **Acomparative Study on the Au/p-Si diodes with and without different rate (0,1, 0,5, 2) ZnO-doped CuO interfacial layer**  
ÇETİNKAYA H. G. , ALTINDAL Ş., DEMİREZEN S.  
International Materials Science and Nanotechnology for Next Generation (MSNG2018), 4 - 07 Ekim 2018
- XVII. **Photocurrent characteristics of Au/ p-Si (MS) type photo-diodewith (2 ZnO-doped CuO)/ Interfacial layer by sol gel method**  
ALTINDAL Ş., ÇETİNKAYA H. G.  
International Materials Science and Nanotechnology for Next Generation (MSNG2018), 4 - 07 Ekim 2018
- XVIII. **On the voltage dependent profiles of surface states and their relaxation times in Al/C<sub>29</sub>H<sub>32</sub>O<sub>17</sub>/p-Si (MPS) structure by using conductance method**  
YÜKSELTÜRK E., ERBİLEN TANRIKULU E., ALTINDAL Ş.  
5th International Conference on Materials Science and Nanotechnology For Next Generation (MSNG2018), 4 - 06 Ekim 2018

- XIX. **Efficiency Restrictions and Characterization In Solar Cells.**  
ALTINDAL Ş.  
5th International conference on materials science and nanotechnology for next generation (MSNG2018), 4 - 06 Ekim 2018
- XX. **Frequency Dependent Dielectric Properties, Electric Modulus and ac Electrical Conductivity of Al/C29H32O17/p type Si (MPS) Structure**  
ERBİLEN TANRIKULU E., YÜKSELTÜRK E., ALTINDAL Ş.  
5th International Conference on Materials Science and Nanotechnology For Next Generation (MSNG2018), 4 - 06 Ekim 2018
- XXI. **A Comparative Study on The Electrical Characteristics of Au/p-Si diodes with and without different rate (0.1, 0.5 and 2) ZnO-doped CuO interfacial layer**  
ÇETİNKAYA H. G. , ALTINDAL Ş., DEMİREZEN S.  
5th International conference on materials science and nanotechnology for next generation (MSNG2018), 4 - 06 Ekim 2018
- XXII. **Frequency Dependent on Electric Properties of Al/TiO<sub>2</sub>-(R-CuWs)/pSi Schottky Diode**  
SEVGİLİ Ö., Şahinkaya M. A. , ORAK İ., ÖZEL F., ALTINDAL Ş.  
Turkish Physical Society 34th International Physich Congress, 5 - 09 Eylül 2018
- XXIII. **The Photovoltaik Properties of Al/TiO<sub>2</sub>/p-Si Schottky Diode**  
SEVGİLİ Ö., Şahinkaya M. A. , ORAK İ., ALTINDAL Ş.  
Turkish Physical Society 34th International Physich Congress, 5 - 09 Eylül 2018
- XXIV. **ANOMALOUS PEAK AND NEGATIVE CAPACITANCE BEHAVIOR IN THE FORWARD BIAS C-V PLOTS OF THE Al/(7 Zn-DOPED PVA)/p-Si (MPS) STRUCTURE**  
ERBİLEN TANRIKULU E., ALTINDAL Ş.  
International Congress on Semiconductor Materials and Devices, 17 - 19 Ağustos 2017
- XXV. **On the profile of temperature dependent main electrical parameters inAl/P3HT/p-Si (MPS) structures at low temperatures**  
YÜKSELTÜRK E., ÇOTUK M., BÜLBÜL M. M. , ALTINDAL Ş., ZEYREK S.  
InternationalCongress on Semiconductor Materials and Devices (ICSMD-2017), Konya, Türkiye, 17 - 19 Ağustos 2017
- XXVI. **Anonalous peak and negative capacitance behaviour in the forward bias c-V plots of the A(7 Zn-doped PVA)/p-Si (MPS) Structure**  
ERBİLEN TANRIKULU E., ALTINDAL Ş.  
International Congress on semiconductor materials and devices, 17 - 19 Ağustos 2017
- XXVII. **Frequency and voltage dependence profiles and some main electrical parameters of the Al/(7 Zn-doped PVA)/p-Si (MPS) structures**  
ERBİLEN TANRIKULU E., ALTINDAL Ş.  
International Congress on semiconductor materials and devices, 17 - 19 Ağustos 2017
- XXVIII. **THE INVESTIGATION OF FREQUENCY AND VOLTAGE DEPENDENCE ON ELECTRIC CHARACTERISTICS OF Al/P3HT/ P-Si (MPS) STRUCTURES**  
YÜKSELTÜRK E., ÇOTUK M., BÜLBÜL M. M. , ALTINDAL Ş., ZEYREK S.  
INTERNATIONAL CONGRESS ON SEMICONDUCTOR MATERIAL AND DEVICES, 17 - 19 Ağustos 2017
- XXIX. **On the Frequency and Voltage Dependence of Dielectric Properties and Electric Modulus in Al/Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>/n-Si (MFS) Capacitors by Using Impedance Spectroscopy Method**  
DURMUŞ P., BİLKAN Ç., ALTINDAL Ş., DÖKME İ.  
4th International conference on materials science and nanotechnology for next generation, 28 - 30 Haziran 2017
- XXX. **Comparative Study on the Frequency Dependent Dielectric Properties of Au/n-SiC Metal-Semiconductor (MS) and Au/Al<sub>2</sub>O<sub>3</sub>/n-SiC Metal-Insulator-Semiconductor (MIS) Structures**  
YÜCEDAĞ İ., ERSÖZ G., DEMİR A., ALTINDAL Ş.  
The 25th annual international conference on composites/nanoengineering (ICCE-25), 16 - 22 Temmuz 2017
- XXXI. **Schottky Diode with Curcumin (C21H20O6) Interfacial Layer**  
DÖKME İ., AYDIN F., Karabulut B., ALTINDAL Ş.

- 4th International conference on materials science and nanotechnology for next generation (MSNG2017), 28 - 30 Haziran 2017
- XXXII. **Effects of J-Ray Irradiation on the C-V and  $G/\omega$ -V Characteristics of Al/SiO<sub>2</sub>/p-Si(MIS) Structures**  
DÖKME İ., DURMUŞ P., ALTINDAL Ş.  
4th International conference on materials science and nanotechnology for next generation (MSNG2017), 28 - 30 Haziran 2017
- XXXIII. **The Au/Polyvinyl Alcohol (Co, Zn-Doped)/n-Type Silicon Schottky Barrier Devices**  
DÖKME İ., DURMUŞ P., ALTINDAL Ş.  
4th International conference on materials science and nanotechnology for next generation (MSNG2017), 28 - 30 Haziran 2017
- XXXIV. **The Electrical Characteristics of Al/TiO<sub>2</sub>-GO/n-Si Schottky Structures**  
DÖKME İ., DURMUŞ P., ALTINDAL Ş.  
4th International conference on materials science and nanotechnology for next generation (MSNG2017), 28 - 30 Haziran 2017
- XXXV. **the investigation of the frequency dependent profile of Te/NaF:CdS/SnO<sub>2</sub> Schottky diodes**  
SEVGİLİ Ö., ALTINDAL Ş., BACAĞIZ E.  
4th international conference on materials science and nanotechnology for next generation, 28 - 30 Haziran 2017
- XXXVI. **Complex Dielectric Constant and Complex Electric Modulus of Al/Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>/p-Si (MFS) Structures as Function of Voltage at Room Temperature**  
ÇETİNKAYA H. G. , ALTINDAL Ş.  
4th International conference on materials science and nanotechnology for next generation (MSNG2017), 28 - 30 Haziran 2017
- XXXVII. **Dielectric Constant, Electric Modulus and Electrical Conductivity in Identically Prepared Diodes of Al/Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>/p-Si (MFS) Structure with Barrier and Thickness Inhomogeneity**  
DURMUŞ P., ÇETİNKAYA H. G. , YILDIRIM M., ALTINDAL Ş., DÖKME İ.  
4th International conference on materials science and nanotechnology for next generation (MSNG2017), 28 - 30 Haziran 2017
- XXXVIII. **Surface States, Series Resistance and Interfacial Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> Layer Effects on the Electrical and dielectric Properties of Al/Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>/p-Si (MFS) Structure**  
ÇETİNKAYA H. G. , YILDIRIM M., DURMUŞ P., ALTINDAL Ş.  
4th International conference on materials science and nanotechnology for next generation (MSNG2017), 28 - 30 Haziran 2017
- XXXIX. **On the Profile of Frequency and Voltage Dependent Interface States and Series Resistance in Au/(Co<sub>3</sub>O<sub>4</sub>-doped PVA)/n-Si Schottky Barrier Diodes (SBDs) at Room Temperature**  
DEMİREZEN S., ALTINDAL Ş.  
4th International conference on materials science and nanotechnology for next generation (MSNG2017), 28 Haziran - 30 Temmuz 2017
- XL. **On the temperature and voltage dependent negative dielectric constant, electric modulus and ac electrical conductivity in the Au/Ti/Al<sub>2</sub>O<sub>3</sub>/n-GaAs (MIS) structures at 1MHz.**  
GÜÇLÜ Ç. Ş. , ÖZDEMİR A. F. , ALTINDAL Ş.  
4th International Conference on Materials Science and Nanotechnology for Next Generation (MSNG-2017), 28 - 30 Haziran 2017
- XLI. **Electrical parameters of Al/p-si (MS) structures with (3 Zn-PVA) interfacial layer using current-voltage and capacitance voltage (C-V) measurements at room temperature**  
ALTINDAL Ş., Karabulut B., USLU H., USLU İ.  
4th International conference on materials science and nanotechnology for next generation, 28 - 30 Haziran 2017
- XLII. **Electrical and Dielectric Properties in identically fabricated Al/Bi<sub>3</sub>Ti<sub>4</sub>O<sub>12</sub>/n-Si (MFS) structures by Capacitance/Conductance-Voltage Measurements**  
ÇETİNKAYA H. G. , ALTINDAL Ş.  
2nd International Advanced and Functional Materials Technologies (AFMAT 2016), 20 - 22 Ekim 2016
- XLIII. **Temperature dependent dielectric properties of Au Ti Al<sub>2</sub>O<sub>3</sub> n GaAs MIS structure in wide voltage**



**range of 6V**

Güçlü Ç. Ş. , ÖZDEMİR A. F. , ALTINDAL Ş.

3st International NANOSCIENCE & NANOTECHNOLOGY FOR NEXTGENERATION (NaNoNG 2016) Conference, 20 - 22 Ekim 2016

- XLIV. **Electrical and Dielectric Properties in identically fabricated Al Bi<sub>3</sub>Ti<sub>4</sub>O<sub>2</sub>In Si MFS structures by Capacitance Conductance Voltage Measurements**  
ÇETİNKAYA H. G. , ALTINDAL Ş.  
2nd international Advanced and Functional Materials Technologies (AFMAT) 2016, 20 - 22 Ekim 2016
- XLV. **Interlayer Thickness Dependent WElectrical Characteristics of Al<sub>3</sub>Zn doped Al PVA p Si MPS structures at Room Temperature**  
Badali Y., Nikravan A., Benli B. B. , ALTINDAL Ş., USLU İ.  
1st International Underground Resources and Energy Conference, Yozgat, Türkiye, 6 - 08 Kasım 2016, ss.84
- XLVI. **Electrical Characterization and Sources of Energy Losses in Solar Cells**  
ALTINDAL Ş., ÇETİNKAYA H. G.  
1st International Underground Resources and Energy Conference, 6 - 08 Ekim 2016
- XLVII. **Electrical characteristics of GaAs AlGaAs Structures in the wide Frequency ranges**  
Bektaş C., GÜNEŞ M., LİŞESİVDİN B., Henini M., ALTINDAL Ş.  
2nd International Congress on The World of Technology and Advanced Materials, Kırşehir, Türkiye, 28 Eylül - 02 Ekim 2016
- XLVIII. **A comparative study on dielectric properties electric conductivity and electrical modulus of Au n SiC structures with three different thickness interfacial Zn doped PVA layers as function of thickness and frequency at room temperature**  
İpa h. e. , Aldharob m. h. a. , Kökçe a., ÖZDEMİR A. F. , USLU İ., ALTINDAL Ş.  
2 nd International Conference on Organic Electronic Material Technologies (OEMT2016), Çanakkale, Türkiye, 17 - 19 Mayıs 2016
- XLIX. **On the dielectric relaxation electric modulus and ac electrical conductivity using impedance spectroscopy method in Au Zn doped PVA n SiC MPS organic structures**  
İpa h. e. , Aldharob m. h. a. , Kökçe a., ÖZDEMİR A. F. , USLU İ., ALTINDAL Ş.  
2 nd International Conference on Organic Electronic Material Technologies (OEMT2016), Çanakkale, Türkiye, 17 - 19 Mayıs 2016
- L. **Influence Of Frequency And Applied Voltage On Dielectric Properties Electric Modulus And Electrical Conductivity In Ag<sub>3</sub>Ru doped PVP n Si Structures**  
Kaya G., Badali Y., Nikravan A., ALTINDAL Ş., USLU İ.  
2 nd International Conference on Organic Electronic Material Technologies (OEMT2016), Çanakkale, Türkiye, 17 - 19 Mayıs 2016
- LI. **The effects of surface states Nss series resistance Rs and interlayer on the current voltage and impedance voltage characteristics in Au n Si Ag Schottky barrier diodes SBDS**  
BİLKAN Ç., ALTINDAL Ş.  
2 nd International Conference on Organic Electronic Material Technologies (OEMT2016), 17 - 19 Mayıs 2016
- LII. **Two diodes model and CdSe PVA interfacial layer effect on the forward bias current voltage I V characteristics of Au CdSe PVA n Si Schottky barrier diodes**  
ALTINDAL Ş., BİLKAN Ç.  
2 nd International Conference on Organic Electronic Material Technologies, 17 - 19 Mayıs 2016
- LIII. **Current Conduction Mechanisms CCMs in Au ZnO n Si Schottky Barrier Diodes in Wide Temperature Range**  
Badali Y., Kaya G., Nikravan A., ALTINDAL Ş., USLU İ.  
2 nd International Conference on Organic Electronic Material Technologies (OEMT2016), Çanakkale, Türkiye, 17 - 19 Mayıs 2016
- LIV. **Determining electrical and dielectric properties dependence on various frequencies of Al ZnS PVA p Si MPS structures**  
BARAZ N., YÜCEDAĞ İ., Azizian Kalandaragh Y., ALTINDAL Ş.

2nd International Conference on Organic Electronic Material Technologies (OEMT2016), 17 - 19 Mayıs 2016

- LVI. **MPS Tipi Schottky Engel Diyotların SED Oda Sıcaklığındaki Elektriksel Özellikleri ve Yalıtkan O<sub>2</sub> Zn katkı PVA Tabakanın Etkisi**  
ERBİLEN TANRIKULU E., ALTINDAL Ş., USLU İ.  
Adım Fizik Günleri V, Eskişehir, Türkiye, 21 - 23 Nisan 2016
- LVI. **Frequency and Voltage Dependence of the Main Electrical Parameters of Au ZnO n Si Structures at Room Temperature**  
Nikravan A., Kaya G., Badali Y., ALTINDAL Ş., USLU İ.  
International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016
- LVII. **The preparation of different Interfaced Zn PVA Structures of Al p Si MPS and Analysis of I V and C G V electrical Characteristics**  
Benli B. B. , ALTINDAL Ş., USLU İ.  
International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016
- LVIII. **On the Forward Bias Anomalous Peak and Negative Capacitance NC in Al ZnO p Si Structures at Room Temperatures**  
Aytimur A., ALTINDAL Ş., USLU İ.  
International Physics Conference at the Anatolian Peak, Erzurum, Türkiye, 25 - 27 Şubat 2016
- LIX. **The Investigation of Electrical Characteristics of Ag Ru Doped PVP n Si Structures as Function of Frequency at Room Temperatures**  
Kaya G., Badali Y., nikravan A., ALTINDAL Ş., USLU İ.  
International Physics Conference at the Anatolian Peak, Erzurum, Türkiye, 25 - 27 Şubat 2016
- LX. **Influence of Frequency and Applied Voltage on Dielectric Properties Electric Modules and Electrical Conductivity in Au Zn n Si Structures**  
badali Y., Nikravan A., Kaya G., ALTINDAL Ş., USLU İ.  
International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016
- LXI. **On the Forward Bias Anomalous Peak and Negative Capacitance NC in Al ZnO p Si Structures at Room Temperature**  
Aytimur A., ALTINDAL Ş., ORAK İ., USLU İ.  
International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016
- LXII. **Frequency and Voltage Dependence of Dielectric ac Electrical conductivity and Electric Modulus Profiles in Al Co<sub>3</sub>O<sub>4</sub> PVA p Si Structures in the Wide Frequency Range**  
BİLKAN Ç., ORAK İ., ALTINDAL Ş.  
International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016
- LXIII. **Frequency and Voltage Dependence Surface States and Series Resistance Profiles in Al Co<sub>3</sub>O<sub>4</sub> PVA p Si Structures from Admittance Measurements**  
ALTINDAL Ş., BİLKAN Ç., Kalandaragh Y. A.  
International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016
- LXIV. **The Investigation of Photocapacitor Properties of Au TiO<sub>2</sub> n Si MIS Type Photodiode by Using Impedance Measurements at Room Temperature**  
ŞAFAK ASAR Y., ALTINDAL Ş.  
International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016
- LXV. **The investigation of photocapacitor properties of Au TiO<sub>2</sub> n Si MIS type photodiode bu using impedance measurements at room temperature**  
ŞAFAK ASAR Y., ALTINDAL Ş.  
International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016
- LXVI. **Influence of Frequency and Applied Voltage on Dielectric Properties Electric Modulus and Electrical Conductivity in Au ZnO n Si Structures**  
Badali Y., Nikravan A., Kaya G., ALTINDAL Ş., USLU İ.  
International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016
- LXVII. **The investigation of photoconducting properties of Au TiO<sub>2</sub> n Si MIS type photodiode by using current voltage characteristics at room temperature**

ŞAFAK ASAR Y., ALTINDAL Ş.

International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016

- LXVIII. **The Investigation of Electrical Characteristics of Ag Ru Doped PVP n Si Structures as Function of Frequency at Room Temperature**

Kaya G., Badali Y., Nikravan A., ALTINDAL Ş., USLU İ.

International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016

- LXIX. **The Investigation of Frequency Dependence of Electrical Parameters of Al P Si Structures With 10 Nm Interfacial Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> Layer**

DURMUŞ P., ALTINDAL Ş., YILDIRIM M.

International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016

- LXX. **The Investigation of Electrical Characteristics in the Au n 4H SiC Structures with Different Thickness of Zn doped PVA Interlayer in the Wide Frequency Range**

Lapa H. E. , KÖKCE A., ORAK İ., ALTINDAL Ş.

International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016

- LXXI. **Interfacial layer thickness effect on the performance of Au Zn doped PVA n 4H SiC MPS structures at room temperature**

lapa H. E. , KÖKCE A., ORAK İ., ALTINDAL Ş.

International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016

- LXXII. **The Investigation of Photoconducting Properties of Au TiO<sub>2</sub> n Si MIS Type Photodiode by Using Current Voltage Characteristics at Room Temperature**

ŞAFAK ASAR Y., ALTINDAL Ş.

International Physics Conference at the Anatolian Peak, 25 - 27 Şubat 2016

- LXXIII. **Farklı Arayüzey Zn PVA tabakalı Au p Si MPS yapıların hazırlanması ve elektriksel özelliklerinin I v ve C G v ölçümleri kullanarak incelenmesi**

Bilge Benli B., ALTINDAL Ş., USLU İ.

21. Yoğun Madde Fiziği Ankara Toplantısı, Ankara, Türkiye, 25 Aralık 2015, ss.108

- LXXIV. **ALD Tekniği ile oluşturulan Au/TiO<sub>2</sub>/n-Si diyotların elektriksel ve foto-iletim özelliklerinin oda sıcaklığında incelenmesi**

ŞAFAK ASAR Y., ALTINDAL Ş.

21. Yoğun Madde Fiziği Ankara Toplantısı, Türkiye, 25 Aralık 2015

- LXXV. **Electrical characteristics and energy density distribution of surface states Nss of Ag perylene n Si Schottky barrier diodes SBDs at room temperature**

BİLKAN M. T. , ZEYREK S., BİLKAN Ç., ALTINDAL Ş.

2nd International Nanoscience and Nanotechnology for Next Generation Conference (NaNoNG) 2015, 29 - 31 Ekim 2015

- LXXVI. **Frequency Dependence of Dielectric Properties and ac Electrical Conductivity of Au Ti Al<sub>2</sub>O<sub>3</sub> n GaAs structures with Different Thicknesses Al<sub>2</sub>O<sub>3</sub> interfacial layer**

GÜCLÜ C., ÖZDEMİR A. F. , ALTINDAL Ş.

2nd International Nanoscience and Nanotechnology for Next Generation Conference (NaNoNG) 2015, 29 - 31 Ekim 2015

- LXXVII. **Electrical Characteristics of Au PPy n Si MPS type Schottky Barrier Diodes SBD as Function of Temperature and Applied Bias Voltage**

GÜMÜŞ A., MARIL E., ALTINDAL Ş.

2nd International Nanoscience and Nanotechnology for Next Generation Conference (NaNoNG) 2015, 29 - 31 Ekim 2015

- LXXVIII. **Comparative Analysis of Temperature dependent Electrical Characteristics of Au PPy n Si MPS type Schottky Diodes SDs at Two Frequencies**

ELİF M., GÜMÜŞ A., ALTINDAL Ş.

2nd International Nanoscience and Nanotechnology for Next Generation Conference (NaNoNG) 2015, 29 Ekim - 28 Mart 2015

- LXXIX. **Study on The Reverse Bias Carrier Transport Mechanism in Au TiO<sub>2</sub> n 4H SiC Structure**

ALTINDAL Ş., YILDIZ D. E.

2nd International Nanoscience and Nanotechnology for Next Generation Conference (NaNoNG) 2015, 29 - 31 Ekim 2015

- LXXX. **On the forward bias negative capacitance and interface traps Dit and series resistance Rs effects in Cr p Si MS contacts with and without PPy interfacial layer at room temperature**  
BİLKAN Ç., GÜMÜŞ A., BİLKAN M. T. , ALTINDAL Ş.  
2nd International Nanoscience and Nanotechnology for Next Generation Conference (NaNoNG) 2015, 29 - 31 Ekim 2015
- LXXXI. **THE FABRICATION OF Au CROSS LINKED PVA n Si Au SCHOTTKY BARRIER DIODES SBDs AND INVESTIGATION THEIR ELECTRICAL CHARACTERISTICS AT ROOM TEMPERATURE**  
LİDA B., BİLKAN Ç., ALTINDAL Ş., ALİ N., YASHAR AZİZİAN K.  
9th INTERNATIONAL PHYSICS CONFERENCE OF THE BALKAN PHYSICAL UNION – BPU9, 24-27 AUGUST 2015, 24 - 27 Ağustos 2015
- LXXXII. **ON THE FREQUENCY AND VOLTAGE DEPENDENCE OF ELECTRICAL OF THE AU B13TI4O12 N SI MFS STRUCTURE IN THE TEMPERATURE RANGE IN THE WIDE FREQUENCIES RANGE AT ROOM TEMPERATURE**  
DURMUŞ P., ŞAHİN C., ALTINDAL Ş.  
9th INTERNATIONAL PHYSICS CONFERENCE OF THE BALKAN PHYSICAL UNION – BPU9, 24-27 AUGUST 2015, 24 - 27 Ağustos 2015
- LXXXIII. **Electrical properties of Au/3 Graphene (GP)-doped PVA/n-Si structures as function of frequency**  
ÇETİNKAYA H. G. , KAYA A., ALTINDAL Ş., ORAK İ.  
International Semiconductor Science and Technology Conference 2015 (ISSTC2015), 11 - 13 Mayıs 2015
- LXXXIV. **Some Electrical Properties of Au/n-Si Structures with and without Graphene doped PVA Interfacial Layer**  
ÇETİNKAYA H. G. , KAYA A., ALTINDAL Ş.  
International Semiconductor Science and Technology Conference 2015 (ISSTC2015), 11 - 13 Mayıs 2015
- LXXXV. **Frequency and voltage-dependent electrical and dielectric properties of Au/Graphene Oxide Calcined/n-Si structures at room temperature**  
ALTINDAL Ş., KAYA A., ÇETİNKAYA H. G. , USLU İ.  
International Semiconductor Science and Technology Conference 2015 (ISSTC2015), 11 - 13 Mayıs 2015
- LXXXVI. **Forward and Reverse Bias Current Voltage Characteristics of Au 0 03 Graphene doped PVA n Si Structures in Dark and under Various Illuminations at room temperature**  
Alıaly S., KAYA A., USLU İ., ALTINDAL Ş.  
International Semiconductor Science Technology Conference, İzmir, Türkiye, 11 - 13 Mayıs 2015, ss.42
- LXXXVII. **Forward and Reverse Bias Current Voltage Characteristics of Au 0 03 graphene doped PVA n Si Structures in Dark and under Various Illuminations at room temperature**  
SAHAR A., KAYA A., USLU İ., ALTINDAL Ş.  
International Semiconductor Science and Technology Conference 2015 (ISSTC-2015), 11 - 13 Mayıs 2015
- LXXXVIII. **Frequency Voltage Dependence Dielectric Properties AC Conductivity of Au GO Doped PbCOO Nanoceramic N Si Capacitors at Room Temperature**  
KAYA A., DEMİREZEN S., ALİALY S., ALTINDAL Ş.  
International Semiconductor Science and Technology Conference 2015 (ISSTC-2015), 11 - 13 Mayıs 2015
- LXXXIX. **On the Profile of Frequency and Voltage Dependent Interface States and Series Resistance in Au Pbcoo Nanoceramic N Si Capacitors by Using Admittance Spectroscopy Method**  
KAYA A., DEMİREZEN S., ALTINDAL Ş., AYTİMUR A.  
International Semiconductor Science and Technology Conference 2015 (ISSTC-2015), 11 - 13 Mayıs 2015
- XC. **Frequency and voltage Dependent electrical and Dielectrical Properties of AU Graphene Oxide Calcined n Si Structures at Room Temperature**  
ALTINDAL Ş., KAYA A., ÇETİNKAYA H. G. , USLU İ.  
International Semiconductor Science Technology Conference, İzmir, Türkiye, 10 - 13 Mayıs 2015, ss.72
- XCI. **Electrical characteristics of GaAs AlGaAs Structures in the wide Frequency and applied bias voltage**

**ranges at room temperature**

GÜNEŞ M., LİŞESİVDİN B., PESEN E., Henini M., ALTINDAL Ş.

1st International Conference on Organic Electronic Material Technologies (OEMT'2015), 25 - 28 Mart 2015

- XCII. A comparative study on the main electrical parameters of Au n Si MS Au biphenyl CuPc n Si and Au biphenylSubs CoPc n Si MPS type Schottky barrier diodes SBDs**  
DEMİR A., YÜCEDAĞ İ., GÜLÇİN E., ALTINDAL Ş., BARAZ N., KANDAZ M.  
1st International Conference on Organic Electronic Material Technologies (OEMT'2015) / 25-28 March 2015, Elazığ, Turkey, 25 - 28 Mart 2015
- XCIII. Temperature and frequency effects on the electrical and dielectric properties of the Ag 9 10 H2BaP n Si Au Sb MIS Schottky structure**  
ÖZERDEN E., KILIÇOĞLU T., TURUT A., TECİMER H., ALTINDAL Ş., OCAK Y. S. , TOMBAK A.  
1st International Conference on Organic Electronic Material Technologies (OEMT'2015) / 25-28 March 2015, Elazığ, Turkey, 25 - 28 Mart 2015
- XCIV. Controlling the electrical characteristics of Au n Si structure with biphenyl CoPc and OHSubsZnPc and without interfacial layer**  
BARAZ N., YÜCEDAĞ İ., AHMET D., GÜLÇİN E., ALTINDAL Ş.  
1st International Conference on Organic Electronic Material Technologies (OEMT'2015) / 25-28 March 2015, Elazığ, Turkey, 25 - 28 Mart 2015
- XCV. Negative Capacitance Behaviour in The Forward Bias of Au ZnO n GaAs Schottky Barrier Diodes SBDs in Dark and Under Various Illumination Levels**  
TAN S. O. , USLU TECİMER H., ORAK İ., TECİMER H., ALTINDAL Ş.  
1st International Conference on Organic Electronic Material Technologies (OEMT'2015) / 25-28 March 2015, Elazığ, Turkey, 25 - 28 Mart 2015
- XCVI. Frequency and voltage dependent profile of dielectric properties electric modulus and ac electrical conductivity in the MS structure with GO doped PBCoO calcined interfacial layer at room temperature**  
KAYA A., DEMIREZEN S., ALTINDAL Ş., USLU İ.  
1st International Conference on Organic Electronic Material Technologies (OEMT'2015) / 25-28 March 2015, Elazığ, Turkey, 25 - 28 Mart 2015
- XCVII. Two diodes model in the forward bias current voltage I V characteristics of AlO 33Ga0 67As n GaAs at room temperature**  
GÜNEŞ M., LİŞESİVDİN B., Henini M., ALTINDAL Ş.  
1st International Conference on Organic Electronic Material Technologies (OEMT'2015), 25 - 28 Mart 2015
- XCVIII. The Frequency Dependent Admittance Measurements of Au ZnO n GaAs Schottky Barrier Diodes SBDs**  
ORAK İ., AKIN B., TECİMER H., USLU TECİMER H., ALTINDAL Ş.  
1st International Conference on Organic Electronic Material Technologies (OEMT'2015) / 25-28 March 2015, Elazığ, Turkey, 25 - 28 Mart 2015
- XCIX. On the temperature and voltage dependence of electrical and dielectric properties of the Au Bi3Ti4O12 n Si MFS structure in the temperature range of 120 380 K**  
CANAN S., DURMUŞ P., ALTINDAL Ş.  
1st International Conference on Organic Electronic Material Technologies (OEMT'2015) / 25-28 March 2015, Elazığ, Turkey, 25 - 28 Mart 2015
- C. The source of negative capacitance and anomalous peak in the forward bias capacitance voltage of Cr p Si Au Schottky barrier diodes SBDs**  
BİLKAN Ç., GÜMÜŞ A., ALTINDAL Ş., BİLKAN M. T.  
1st International Conference on Organic Electronic Material Technologies (OEMT'2015) / 25-28 March 2015, Elazığ, Turkey, 25 - 28 Mart 2015
- CI. The Energy Density Distribution Profile of Interface Traps and Their Relaxation times and Capture Cross Sections of MS structure with GO doped PBCoO nanoceramic Structure in Forward and Reverse Bias Regions**

ALTINDAL Ş., KAYA A., Demirezen S., USLU İ.

1st International Conference on Organic Electronic Material Technologies (OEMT'2015) 25-28 March 2015, Elazığ, Türkiye, 25 - 28 Mart 2015, ss.140

- CII. **Frequency and Voltage Dependent profile of Dielectric properties electric modulus and ac electrical conductivity in the MS**  
KAYA A., Demirezen S., ALTINDAL Ş., USLU İ.  
1st International Conference on Organic Electronic Material Technologies (OEMT'2015) 25-28 March 2015, Elazığ, Türkiye, 25 - 28 Mart 2015, ss.74
- CIII. **Illumination Effects on Current Voltage Characteristics of Au ZnO n GaAs Schottky Barrier Diodes SBDs**  
ÇİÇEK O., USLU TECİMER H., ORAK İ., TECİMER H., ALTINDAL Ş.  
1st International Conference on Organic Electronic Material Technologies (OEMT'2015) / 25-28 March 2015, Elazığ, Turkey, 25 - 28 Mart 2015
- CIV. **AuZn TiO<sub>2</sub> p GaAs 110 Schottky Bariyer Diyotlarda Dielektrik ve Empedans Spektroskopisi**  
ŞAFAK ASAR Y., ASAR T., ÖZÇELİK S., ALTINDAL Ş.  
20. Yoğun Madde Fiziği Ankara Toplantısı, Ankara, Türkiye, 26 Aralık 2014, ss.79
- CV. **Au/TiO<sub>2</sub>/n-Si Diyotlarda aydınlatma şiddetinin doğru ve ters beslem C-V ve G/ω-V karakteristikler üzerine etkisinin incelenmesi**  
ALTINDAL Ş., ŞAFAK ASAR Y., ORAK İ.  
21. Yoğun Madde Fiziği Ankara Toplantısı, Türkiye, 25 Aralık 2015
- CVI. **On the Temperature and Voltage Dependence Forward Bias Current-Voltage (I-V) Characteristics in Au/Ca<sub>3</sub>Co<sub>4</sub>Ga<sub>0.0010x</sub>(2 graphene cobalt)/n-Si Structure**  
MARIL E., KAYA A., ÇETİNKAYA H. G. , KOÇYİĞİT S., ALTINDAL Ş.  
Nanoscience Nanotechnology for Next Generation (NanoNGe'14), 20 - 22 Ağustos 2014
- CVII. **Temperature and Voltage Dependence of Electrical and Dielectric Properties of Au/1 graphene doped- Ca<sub>1.9</sub>Pr<sub>0.1</sub>Co<sub>4</sub>O<sub>x</sub>/n-Si Structure**  
ÇETİNKAYA H. G. , KAYA A., ALTINDAL Ş., KOÇYİĞİT S.  
Nanoscience Nanotechnology for Next Generation (NanoNGe'14), 20 - 22 Ağustos 2014
- CVIII. **On the Origin of Capacitance and Anomalous Peak in the Forward Bias Capacitance-Voltage plots in Au/1 graphene doped-Ca<sub>1.9</sub>Pr<sub>0.1</sub>Co<sub>4</sub>O<sub>x</sub>/n-Si Structure.**  
ÇETİNKAYA H. G. , ALTINDAL Ş., KAYA A., KOÇYİĞİT S.  
Nanoscience Nanotechnology for Next Generation, 20 - 22 Ağustos 2014
- CIX. **Investigation of Negative Dielectric Constant at Forward Biases Using Impedance Spectroscopy Analysis in Au/1 graphene doped- Ca<sub>1.9</sub>Pr<sub>0.1</sub>Co<sub>4</sub>O<sub>x</sub>/n-Si Structure**  
ÇETİNKAYA H. G. , ALİALY S., ALTINDAL Ş., USLU İ., KAYA A.  
Nanoscience Nanotechnology for Next Generation, 20 - 22 Ağustos 2014
- CX. **The energy density distribution of interface states in AuZn TiO<sub>2</sub> p GaAs 110 MIS schottky barrier diodes using admittance spectroscopy**  
ŞAFAK ASAR Y., ALTINDAL Ş.  
Türk Fizik Derneği 31. Uluslararası Fizik Kongresi, 21 - 24 Temmuz 2014
- CXI. **The frequency dependence properties of tan M and M in the wide frequency range in AuZn TiO<sub>2</sub> p GaAs 110 schottky barrier diodes**  
ŞAFAK ASAR Y., ALTINDAL Ş.  
Türk Fizik Derneği 31. Uluslararası Fizik Kongresi, 21 - 24 Temmuz 2014
- CXII. **The evaluation of Surface States Barrier Height and Series Resistance in Au CdTe Schottky Barrier Diodes SBDs at Moderate Temperatures**  
ŞAFAK ASAR Y., ALTINDAL Ş., MEMMEDLİ T., KANBUR ÇAVUŞ H.  
Türk Fizik Derneği 28. Uluslararası Fizik Kongresi, 6 - 09 Eylül 2011
- CXIII. **On the Energy Density Distribution Profile of surface States in Al pentacene p GaS<sub>a</sub> Heterojunction Diodes**  
ŞAFAK ASAR Y., YAKUPHANOĞLU F., ALTINDAL Ş.

Mini-Workshop on Surface Science for Inauguration of the Turkish Surface Science Society, Türkiye, 23 Mayıs 2011

- CXIV. **Illumination Dependent Admittance Characteristics of Au/Zinc Acetate Doped Polyvinyl Alcohol (PVA:Zn)/n-Si Schottky Barrier Diodes (SBDs)**  
Tascioglu I., AYDEMİR U., Altındal Ş., Tunc T.  
1st International Congress on Advances in Applied Physics and Materials Science (APMAS), Antalya, Türkiye, 12 - 15 Mayıs 2011, cilt.1400, ss.307-311
- CXV. **Illumination Effect on Admittance Measurements of Polyvinyl Alcohol (Co, Zn-Doped)/n-Si Schottky Barrier Diodes in Wide Frequency and Applied Bias Voltage Range**  
Yeriskin S. A., Uslu H., Tunc T., ALTINDAL Ş.  
1st International Congress on Advances in Applied Physics and Materials Science (APMAS), Antalya, Türkiye, 12 - 15 Mayıs 2011, cilt.1400, ss.541-545
- CXVI. **The determination of frequency and applied bias voltage of electrical and dielectric properties of Al SiO<sub>2</sub> p Si MOS structures**  
ALTINDAL Ş., ŞAFAK ASAR Y., SÖNMEZ Z., KAYA A.  
Türk Fizik Derneği 27. Uluslararası Fizik Kongresi, 14 - 17 Eylül 2010
- CXVII. **The determination of energy density distribution profile of interface states in Al SiO<sub>2</sub> p Si MOS structures**  
ŞAFAK ASAR Y., ALTINDAL Ş., Sönmez Z., KAYA A.  
Türk Fizik Derneği 27. Uluslararası Fizik Kongresi, 14 - 17 Eylül 2010
- CXVIII. **Temperature Dependent Electrical Characteristics of AlGaAs/GaAs Single-Quantum-Well Lasers Using C-V and G/w-V Measurements**  
ÖZÇELİK S., USLU H., BENGİ A., ÇETİN S. Ş., AYDEMİR U., ALTINDAL Ş., MAMMADOV T.  
XXI International Scientific and Engineering Conference on Photoelectronics and Night Vision Devices, Moskva, Rusya, 25 - 28 Mayıs 2010
- CXIX. **Au/TiO<sub>2</sub>/n-Si Schottky Diyotlarında Ara-yüzey Durum Analizi**  
ALTUNTAŞ H., YILDIZ A., ÖZEN Y., ALTINDAL Ş., ÖZÇELİK S.  
16. Yoğun Madde Fiziği Kongresi (YMF16), Ankara, Türkiye, 06 Kasım 2009
- CXX. **Au SrTiO<sub>3</sub> n Si Yapısındaki Derin Seviyelerin Tavlama Bağı DLTS Metodu ile Karakterizasyonu**  
AYDEMİR U., TAŞÇIOĞLU İ., ASAR T., ŞAFAK Y., ALTINDAL Ş., MAMMADOV T. S., ÖZÇELİK S.  
16. Yoğun Madde Fiziği Ankara Toplantısı, Ankara, Türkiye, 06 Kasım 2009, ss.92
- CXXI. **Interface state density analyzing of Au TiO<sub>2</sub> rutile n Si Schottky barrier diode**  
Altuntaş H., Bengi A., Asar T., Aydemir U., Sarıkavak B., Özen Y., Altındal Ş., Özçelik S.  
13th European Conference on Applications of Surface and Interface Analysis, Antalya, Türkiye, 18 - 23 Ekim 2009, ss.322
- CXXII. **The effect of insulator layer thickness on the main electrical parameters in Ni Au Al<sub>x</sub>Ga<sub>1-x</sub>N AlN GaN heterostructures**  
ALTINDAL Ş., ŞAFAK ASAR Y., TAŞÇIOĞLU İ., ÖZBAY E.  
13th European Conference on Applications of Surface and Interface Analysis, 18 - 23 Ekim 2009
- CXXIII. **Interface States Density Analyzing of Au/TiO<sub>2</sub> (Rutile)/n-Si Schottky Barrier Diode**  
ALTUNTAŞ H., BENGİ A., ASAR T., AYDEMİR U., SARIKAVAK B., ÖZEN Y., ALTINDAL Ş., ÖZTÜRK M., ÖZÇELİK S.  
13th European Conference on Applications of Surface and Interface Analysis, Antalya, Türkiye, 18 - 23 Ekim 2009
- CXXIV. **Deep level transient spectroscopy of Au SrTiO<sub>3</sub> n Si structures**  
AYDEMİR U., ŞAFAK ASAR Y., ALTINDAL Ş.  
Türk Fizik Derneği 26. Uluslararası Fizik Kongresi, 24-27 Eylül 2009, 24 - 27 Eylül 2009
- CXXV. **The Role of Interface states and Series Resistance on the Current Voltage I V Characteristics of Au n CdTe Solar cells**  
FİAT VAROL S., MERDAN Z., ALTINDAL Ş., Mammadov T.  
25. Uluslararası Fizik Kongresi, 25 - 29 Ağustos 2008
- CXXVI. **Frequency and Voltage Dependent series resistance profile in Au n CdTe Solar cells**  
FİAT VAROL S., MERDAN Z., ALTINDAL Ş., Mammadov T.

25. Uluslararası Fizik Kongresi, Bodrum, Türkiye, 25 - 29 Ağustos 2008

CXXVII. ON THE PROFILE OF  $6^{\circ}\text{Co}$   $\gamma$ -RAY IRRADIATION DEPENDENT INTERFACE STATES AND SERIES RESISTANCE IN  $\text{Al/SiO}_2/\text{p-Si}$  (MIS) STRUCTURES

ALTINDAL Ş., TAŞÇIOĞLU İ., ÖZBAY A.

5. Uluslararası Bilim Teknik Konferansı: Fiziğin Güncel Problemleri, 25 - 27 Haziran 2008

## Desteklenen Projeler

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje,  $\text{Au/n-CdTe}$  Schottky Diyotların Elektriksel Özelliklerinin Karanlık ve Işık Altında İncelenmesi, 2009 - Devam Ediyor

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje,  $\text{Au/BTO/SiO}_2/\text{Si}$  (MFIS) Yapıların Hazırlanması Elektriksel Ve D+D50ielektrik Özelliklerinin Sıcaklık ve Frekansa Bağlı İncelenmesi, 2008 - Devam Ediyor

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje,  $\text{Au/n-InP}$  ve  $\text{Au/n-GaN}$  Schottky Diyotlarının Hazırlanması, Elektriksel ve Dielektrik Özelliklerinin Sıcaklığa ve Frekansa Bağlı İncelenmesi, 2007 - Devam Ediyor

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje, Geniş Bant Araklı Metal-Yarıiletken(MS) Yapıların Hazırlanması ve Temel Parametrelerinin Sıcaklık ve Radyasyon Dozuna Bağlı İncelenmesi, 2006 - Devam Ediyor

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje, MOS Yapılarının Hazırlanması ve Temel Özelliklerinin Radyasyon ve Frekansa Bağlı İncelenmesi, 2003 - Devam Ediyor

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje, MIS Yapıların Hazırlanması ve Onların Akım İletim Mekanizmalarının İncelenmesi, 2002 - Devam Ediyor

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje, BTO amorf filmlerde dielektrik sabitinin sıcaklık ve kalınlığa bağlı inc., 2001 - Devam Ediyor

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje, MOS yapılarında dielektrik sabitinin frekans, kalınlık ve sıcaklığa bağlı incelenmesi, 2000 - Devam Ediyor

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje, Schottky diyotlarında ara yüzey durumlarının C-V karakterisliklerine etkisi, 1999 - Devam Ediyor

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje, Güneş pilleri schottky diyodları ve MOS yapımı ve tenel parametrelerinin sıcaklığa bağlı incelenmesi, 1998 - Devam Ediyor

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje, Yarı iletken ve ferro yarıiletken Materyallerin optik ve elektriksel karakteristiklerinin sıcaklığa bağlı olarak incelenmesi, 1996 - Devam Ediyor

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje, Yarı iletken kristaller için ısı kontrolü oksidasyon fırınının yapımı., 1995 - Devam Ediyor

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje,  $\text{Au/metal-PVA/n-Si/Au}$  (MPS) tipi yapıların hazırlanması ve elektriksel özelliklerinin frekans ve voltaja bağlı oda sıcaklığında incelenmesi, 2016 - 2017

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje,  $\text{Au/Zn-Katkılı/n-GaAs}$  Yapıların Hazırlanması ve Fiziksel Özelliklerinin İncelenmesi, 2012 - 2013

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje,  $\text{Au/TiO}_2/\text{n-SiC}$  (MIS) Schottky Diyotlarının Hazırlanması ve Elektriksel Özelliklerinin incelenmesi, 2011 - 2012

ALTINDAL Ş., Yükseköğretim Kurumları Destekli Proje, Metal/katkılı PVA/Yarıiletken Yapılarının Radyasyona Bağlı İncelenmesi, 2010 - 2012

## Atıflar

Toplam Atıf Sayısı (WOS):7434

h-indeksi (WOS):46